

Engineering electron-phonon interactions in noble metals with nanoscale interfaces

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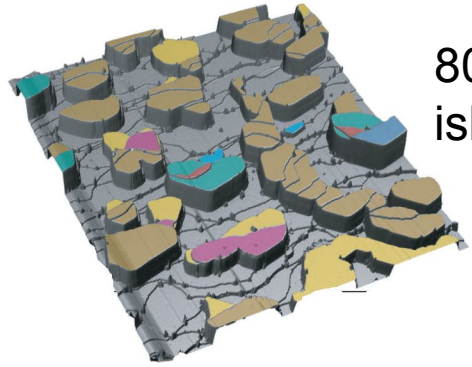


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MINISTRY OF
EDUCATION



Modulating electron-phonon interaction in metals

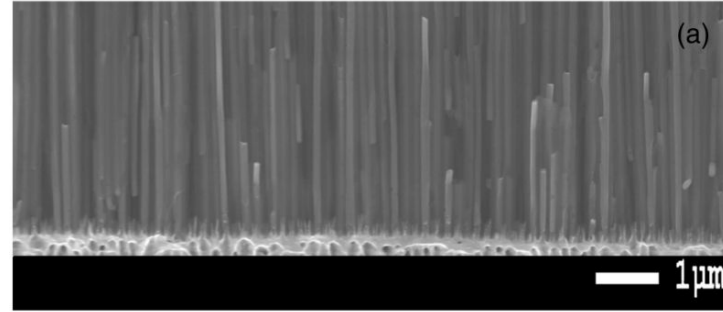
Aligning states in a quantum well with fermi level



800 nm² Pb islands on Cu

Phys. Rev. Lett. **114**, 047002

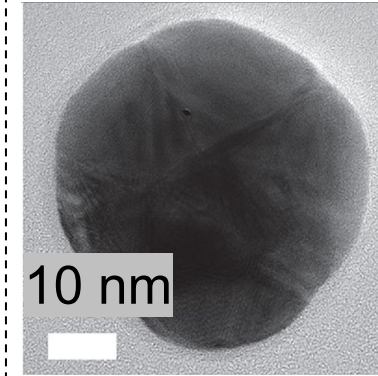
Achieving low-frequency phonons with surfaces



50 nm Sn nanowires

Phys. Rev. B **99**, 064512

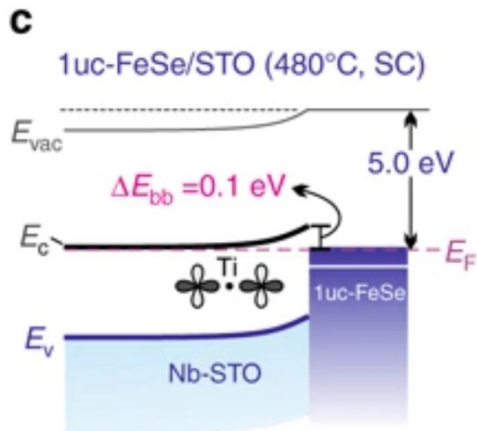
Electron scattering from surfaces



Polycrystalline Au nanoparticles

ACS Photonics **2021**, *8*, *3*, 752–757

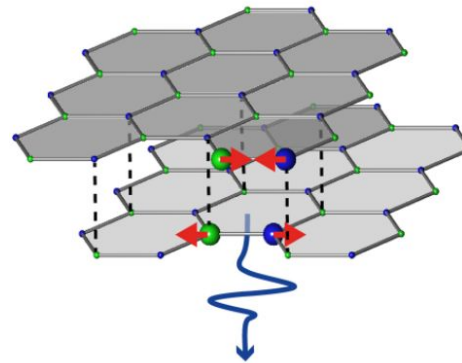
Interfacial el-ph interaction



SrTiO₃ on FeSe

Nat Commun **8**, 214 (2017)

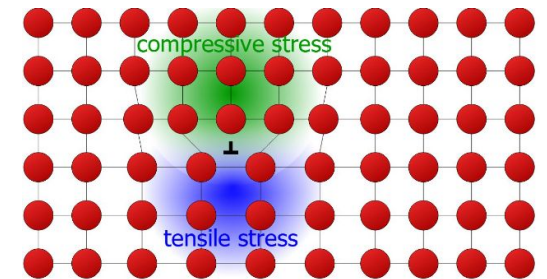
Optically driving the lattice



THz spectroscopy in bilayer graphene

Phys. Rev. B **95**, 024304

Stress

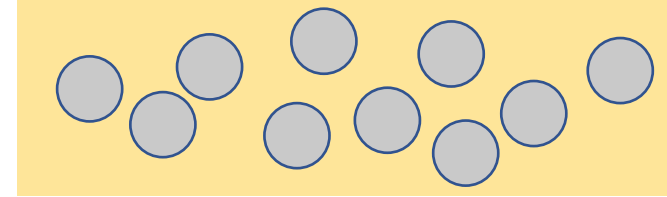


Proc. Natl. Acad. Sci. **2014**, *111*, 8712–8716

Our approach

Dense network of nanoscale crystalline interfaces

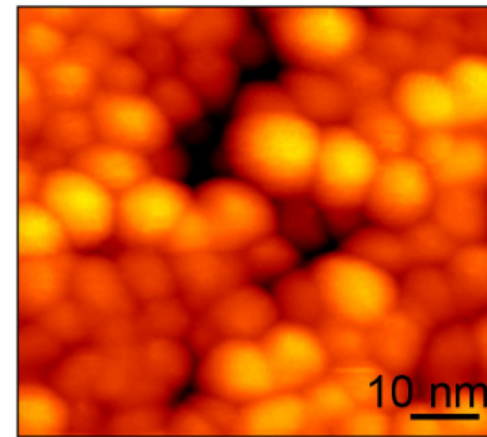
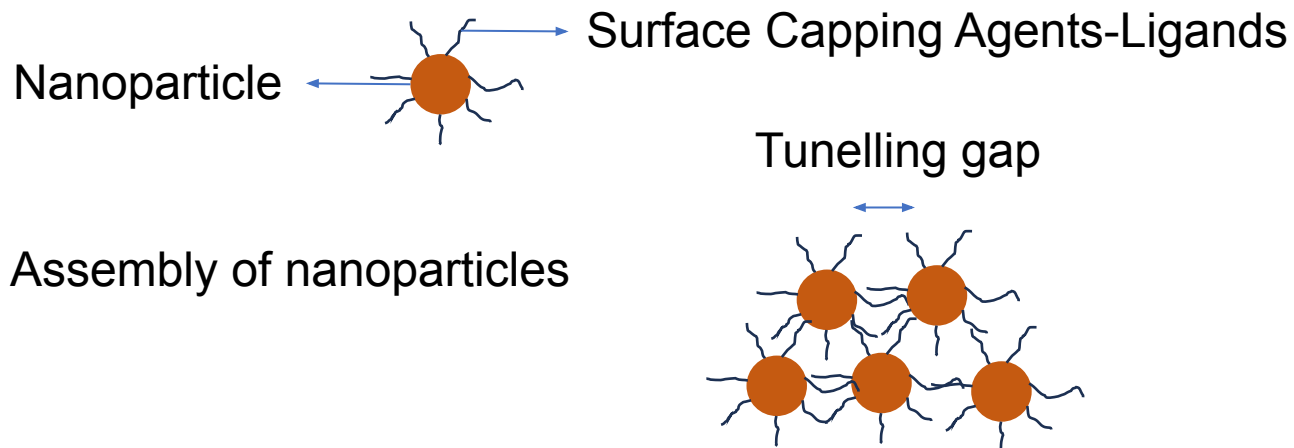
Metal nanoparticles embedded inside a metallic matrix



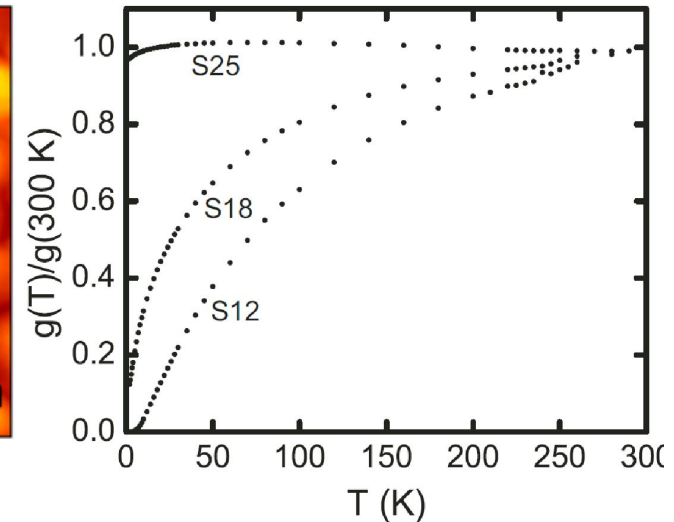
Challenge

Not achieved: Bottom-up assembly of 'Metal' with nanoparticles

Electron tunneling effects: Coulomb blockade, Variable Range hopping, Activated transport

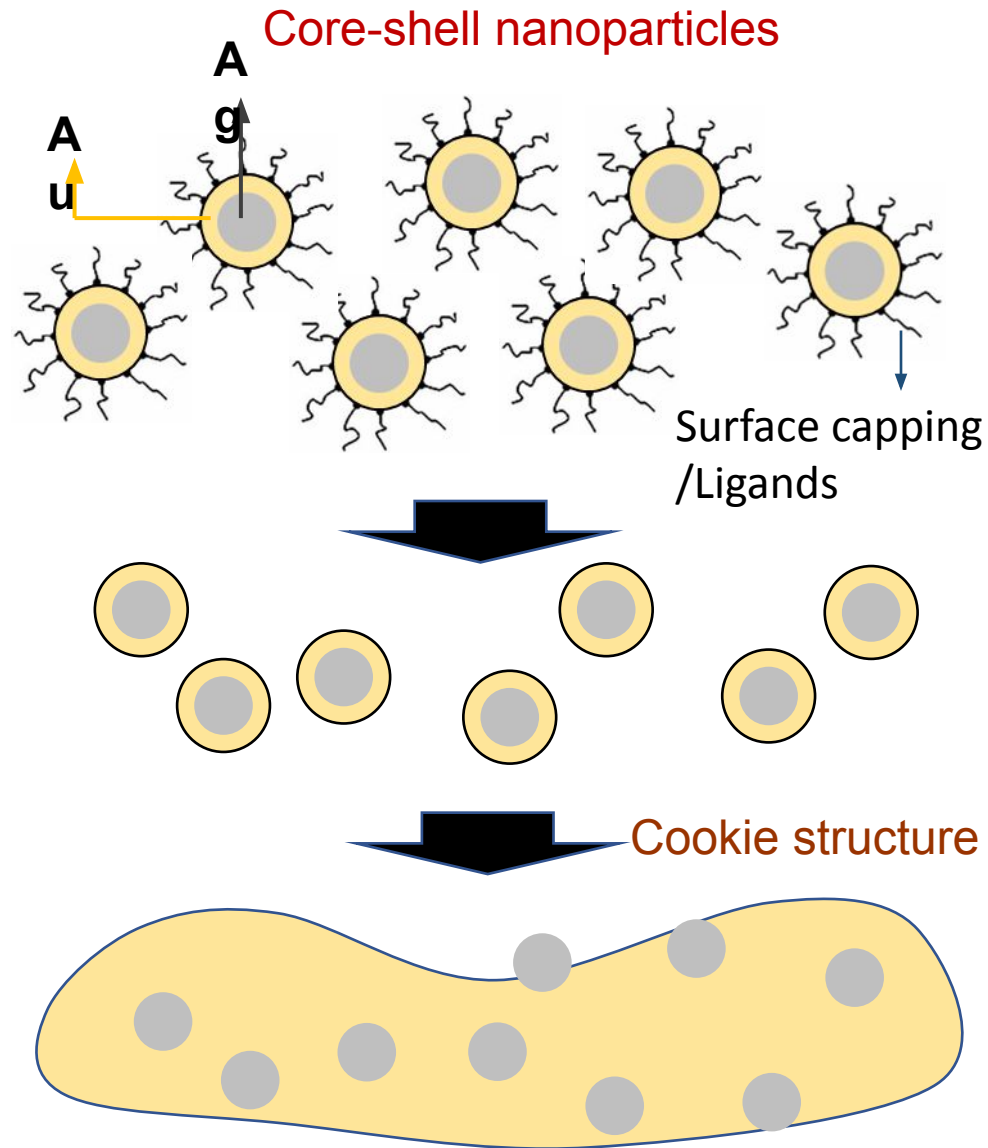


Au nanoparticles



Phys. Rev. B 89, 155117 (2014)

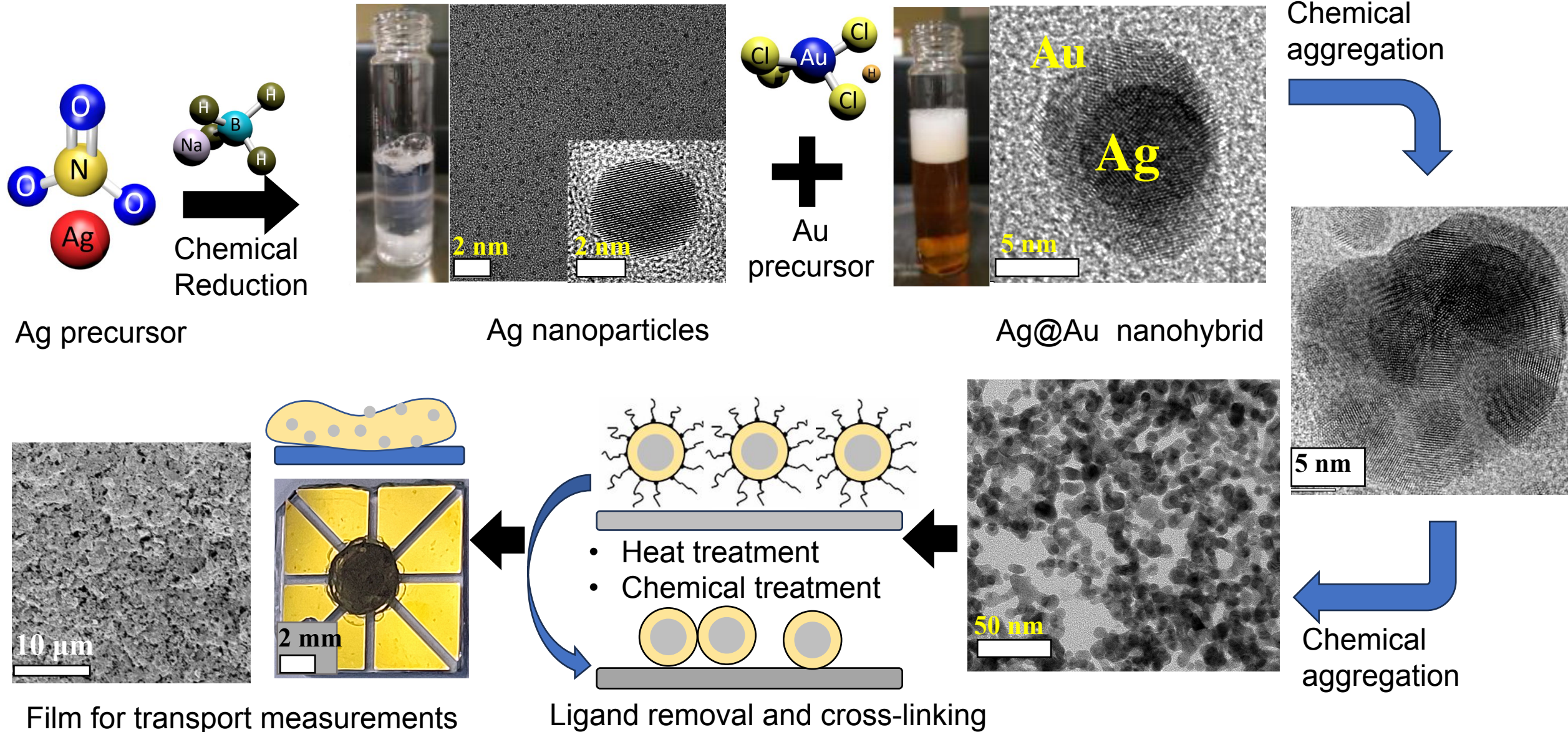
Our approach: A bi-metallic nano-hybrid



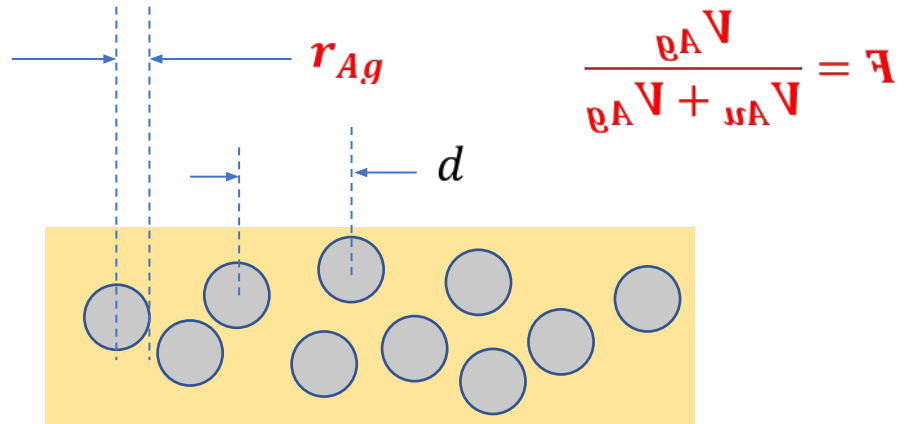
Near identical lattice constants of Au and Ag
: 4.078 Å and 4.085 Å

Chemical route – The process flow

Ag(NP) – Au hybrid

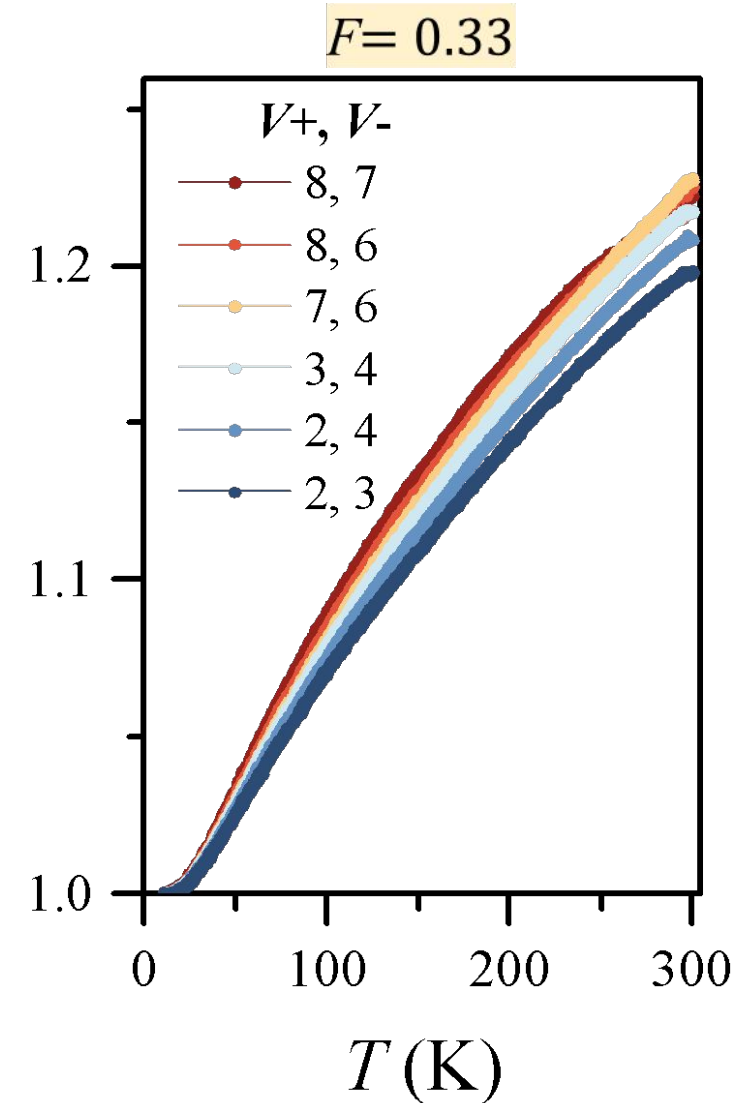
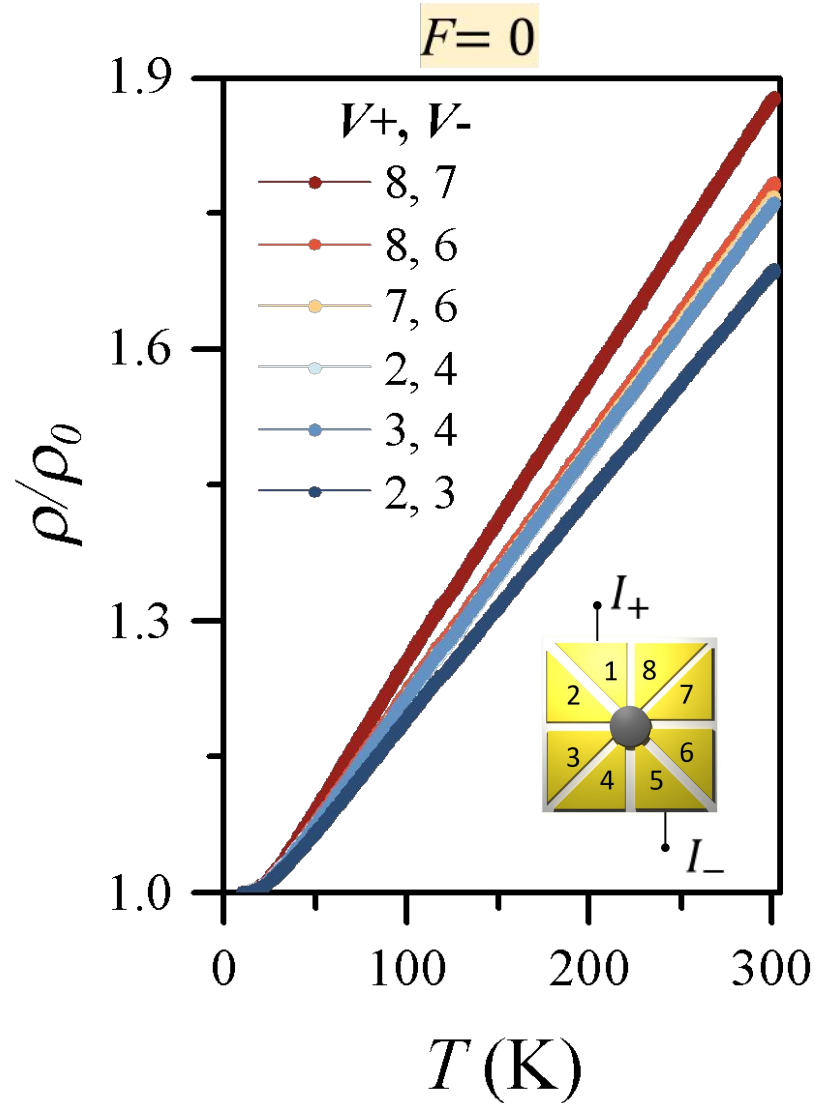


Temperature-dependance of electrical resistivity



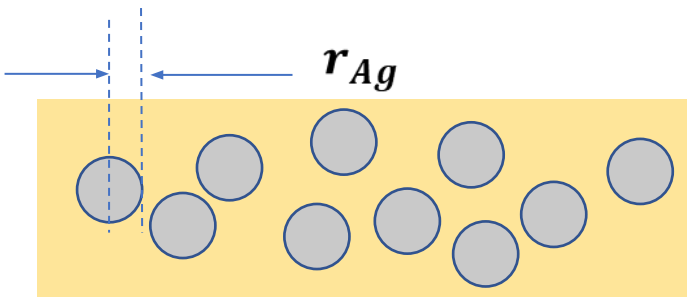
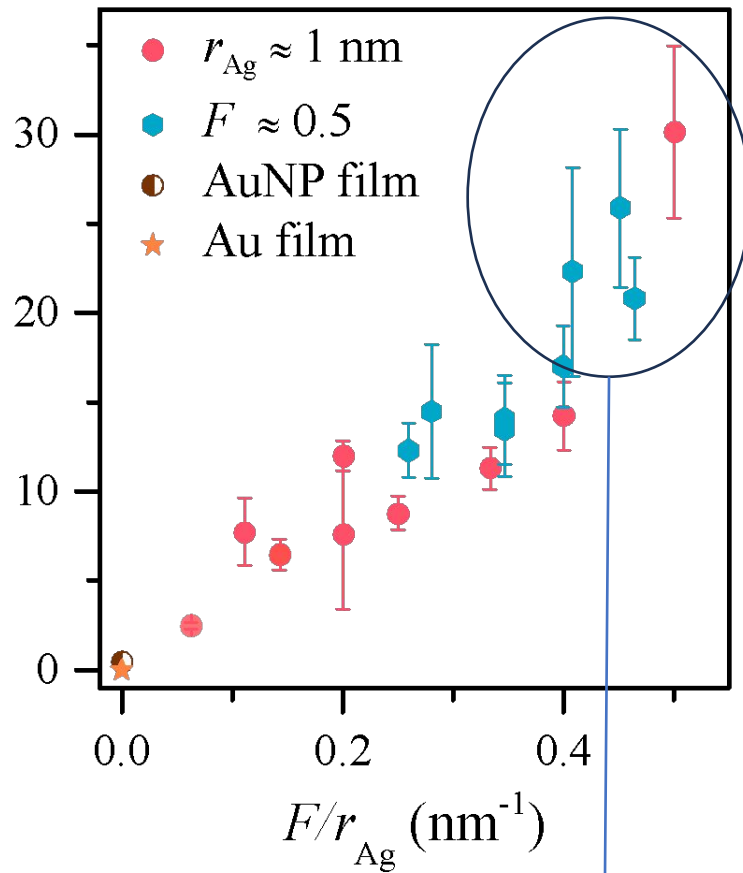
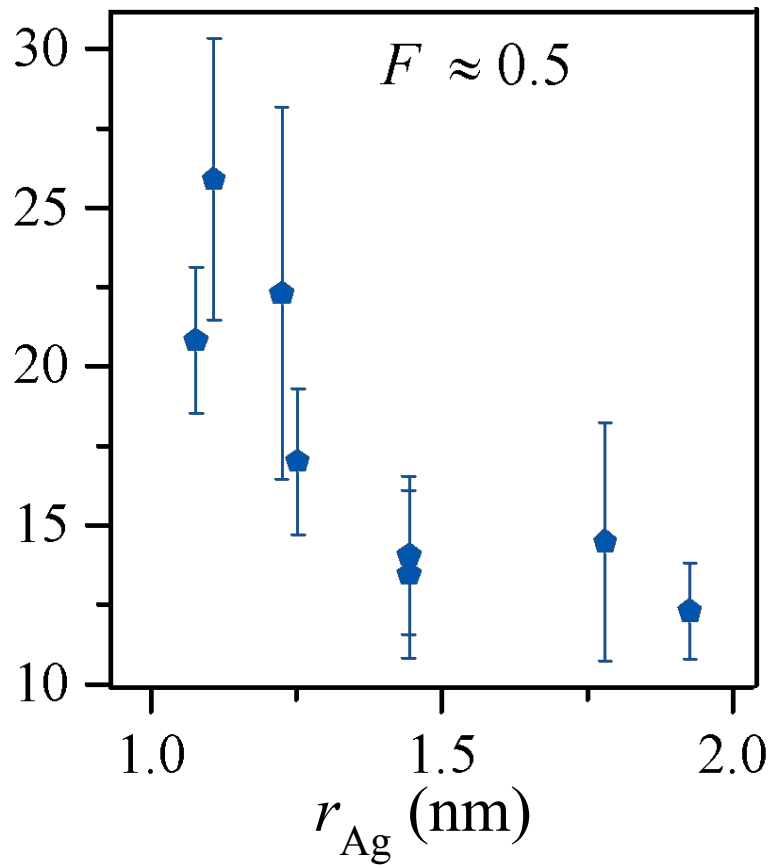
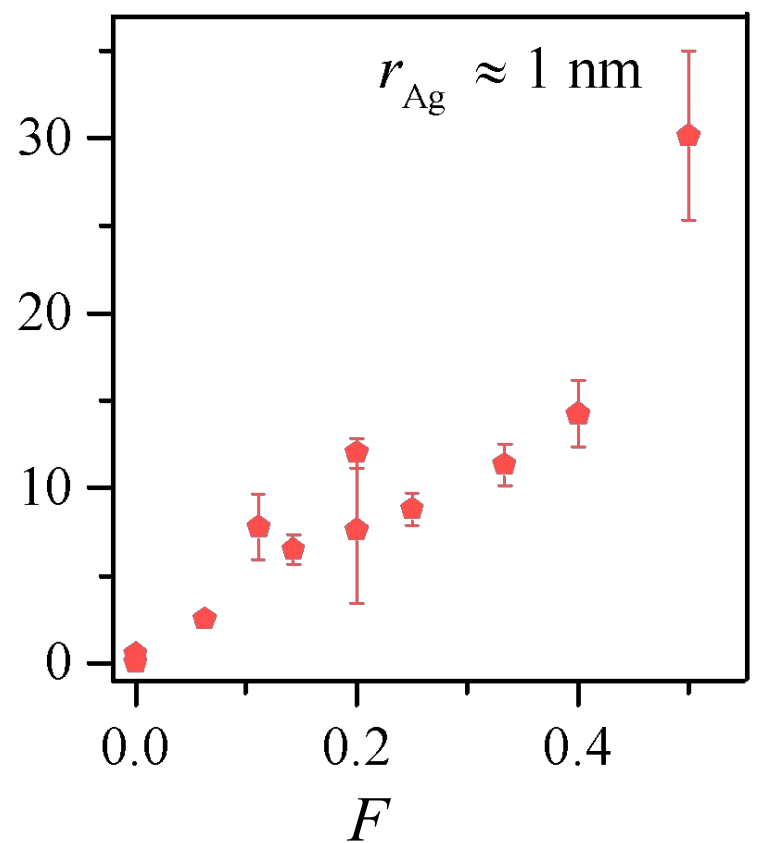
- r_{Ag} : AgNP radius $\sim 1 - 3$ nm
- d : AgNP distance $\sim 3 - 6$ nm

- Homogenous metallic transport
- Saturation of resistivity for $F > 0$



Resistivity – interface correlation

ρ_0 : Resistivity at base temperature ~ 4 K



$$\frac{\rho_{Ag} V}{\rho_{Ag} V + \rho_{Au} V} = F$$

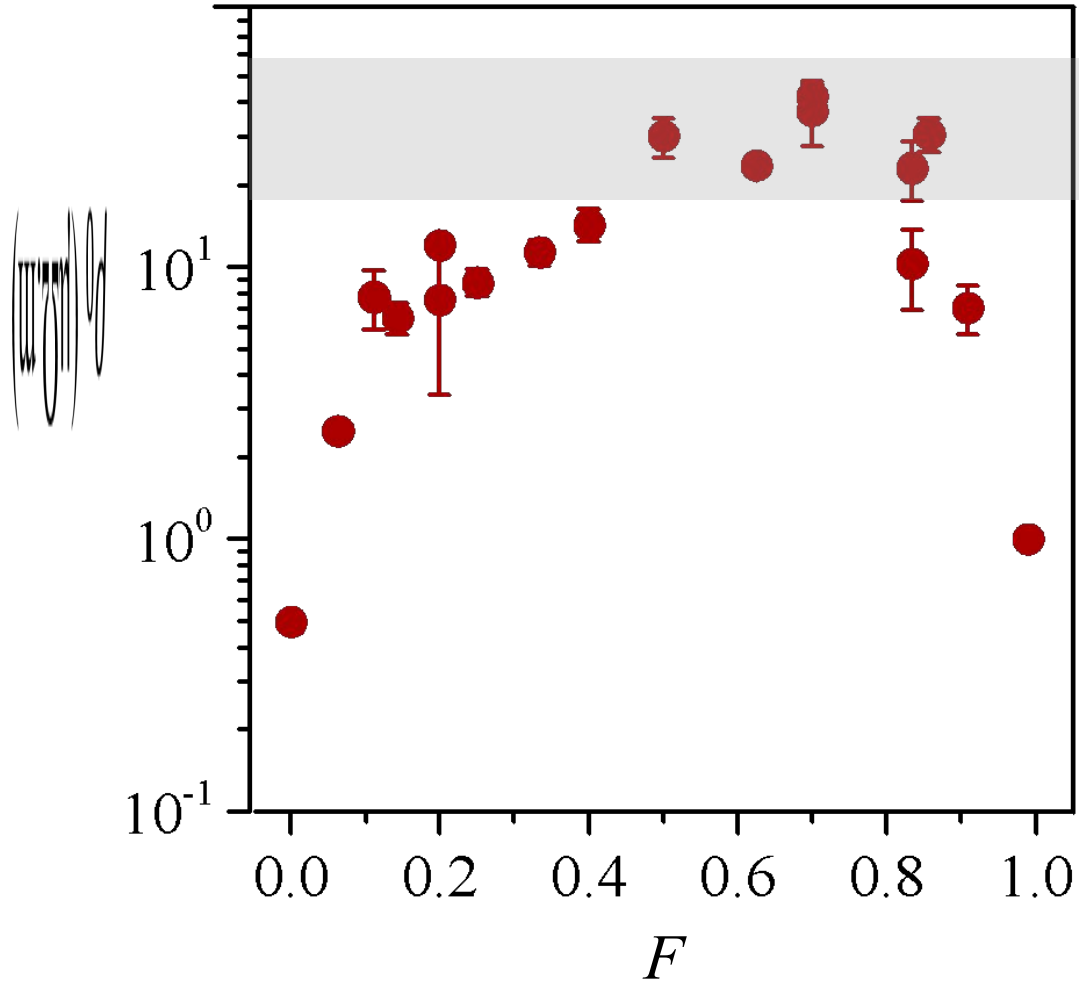
Interface area of Ag per unit volume: F/r_{Ag}

Increasing residual resistivity with overall interface area of Ag

Mott-Ioffe-Regel limit!

The Mott-Ioffe-Regel (MIR) Limit and 'bad metals'

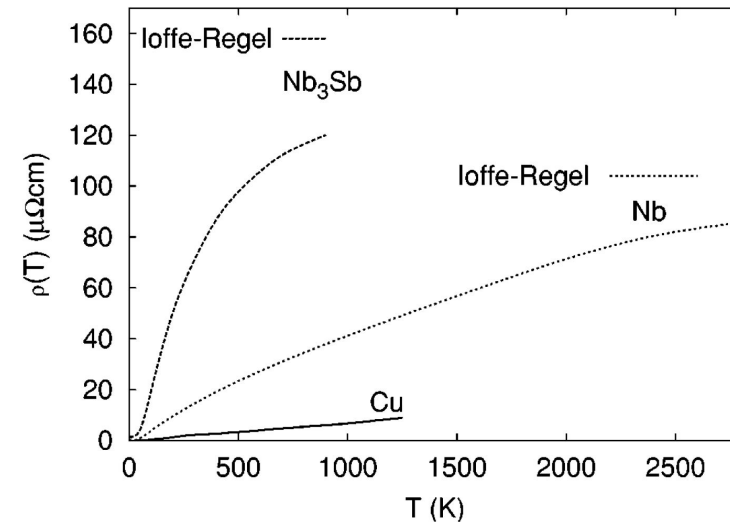
$$\frac{\rho_A V}{\rho_A V + \mu_A V} = \eta$$



MIR Limit: $k_F l = 1$ $\rho_{MIR}^{Au} = 24.6 \mu\Omega\text{-m}$

$$\rho_{MIR} = \frac{\hbar^2 \pi \epsilon}{e^2 k_F} = \frac{\hbar^2 \pi \epsilon}{(J_F \lambda_F) e^2 k_F} = \eta_{MIR} \rho$$

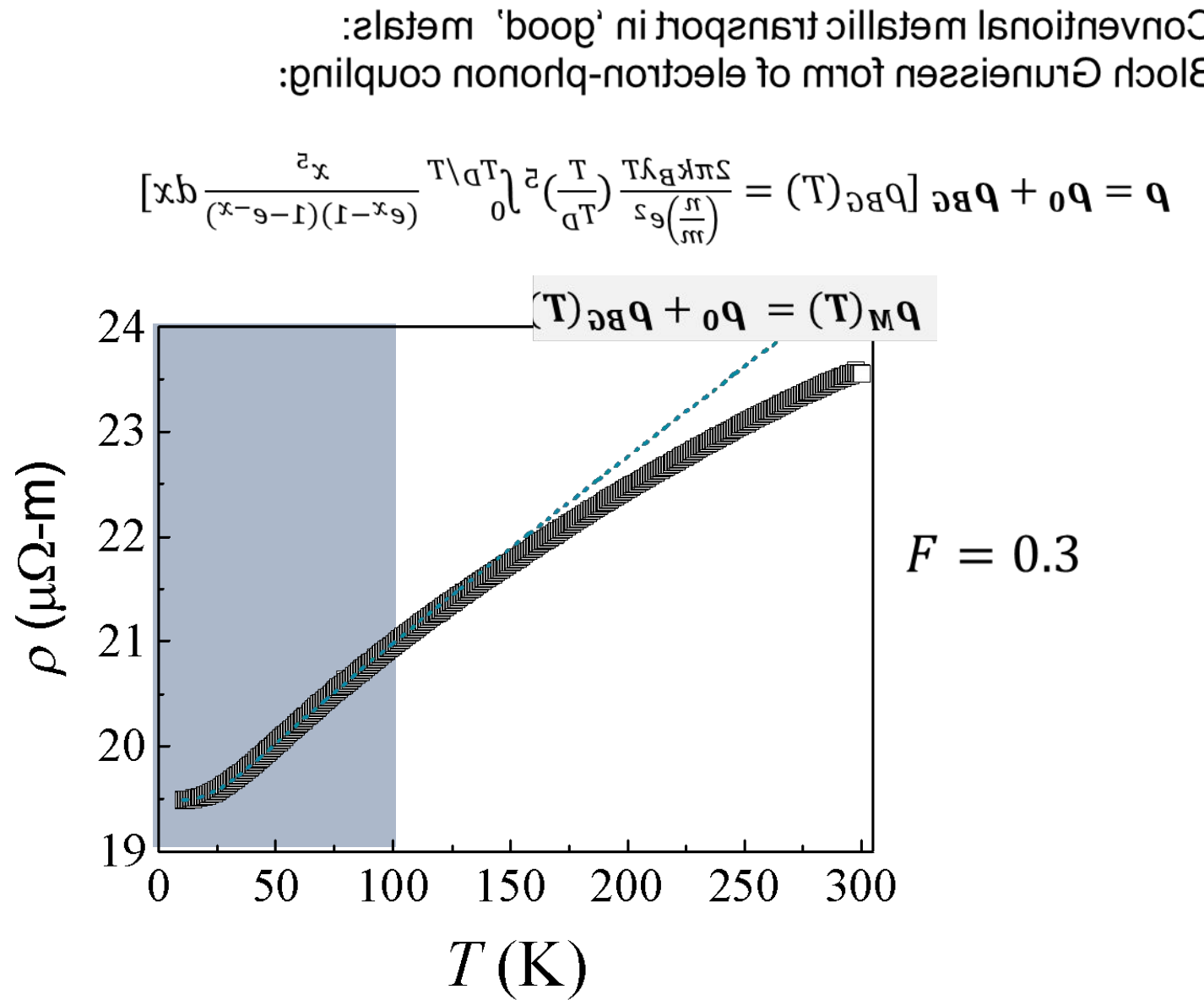
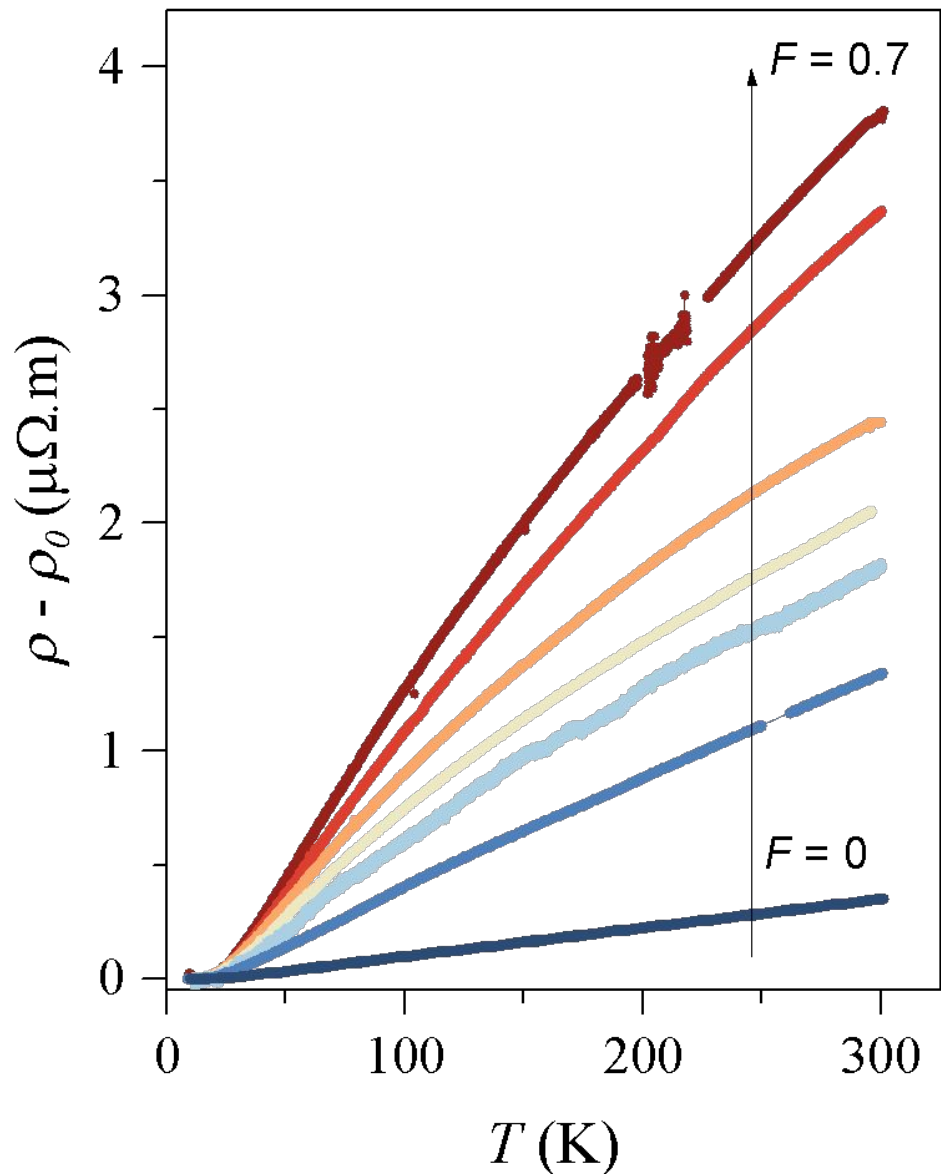
- Mean-free path approaching inter-atomic distance
- Ill-defined quasiparticles



Gunnarsson, Calandra, Han Rev Mod Phys 2003 75, 1085

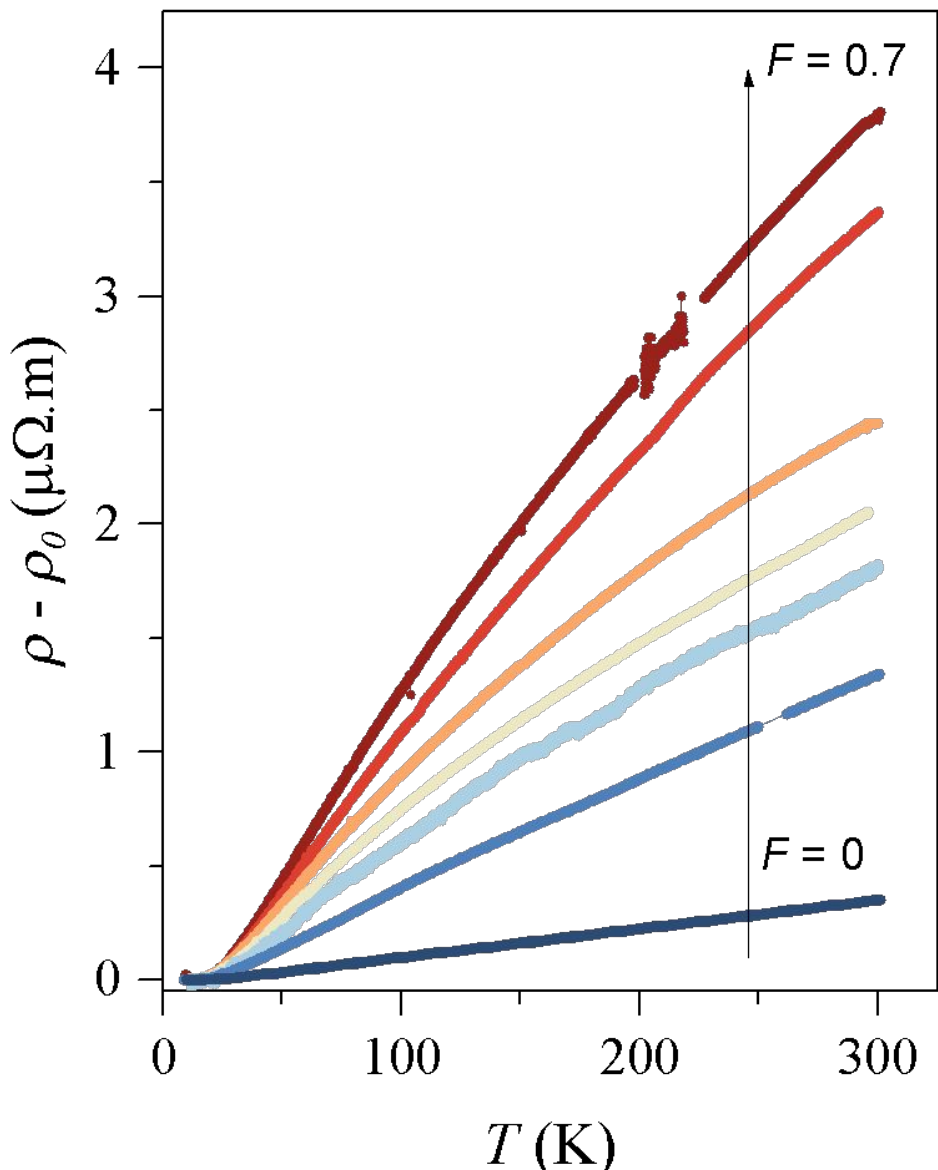
Resistivity saturation

The Mott-Ioffe-Regel (MIR) Limit and 'bad metals'



Resistivity saturation

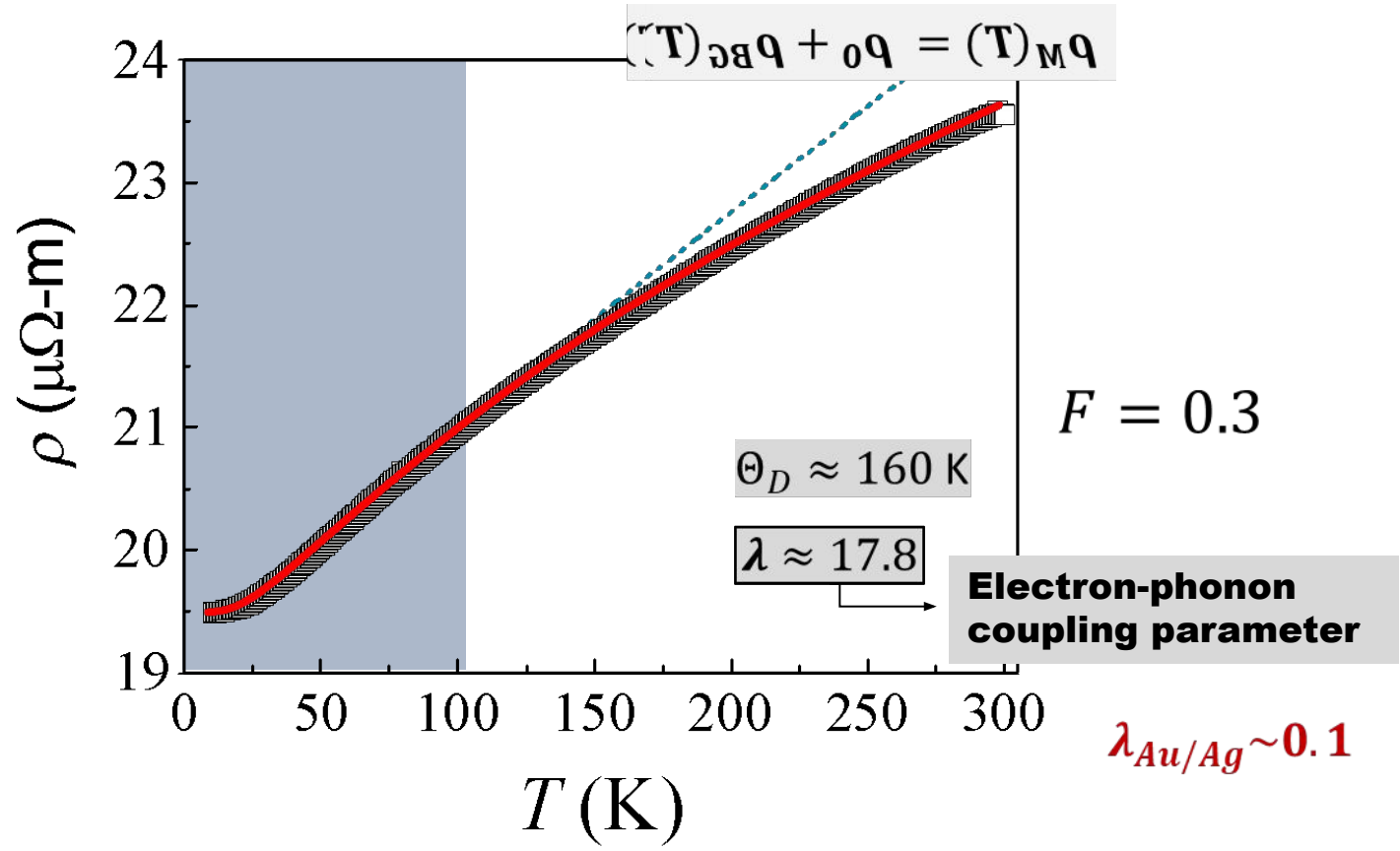
The Mott-Ioffe-Regel (MIR) Limit and 'bad metals'



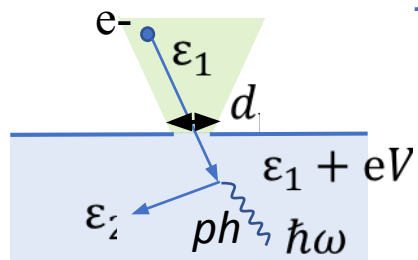
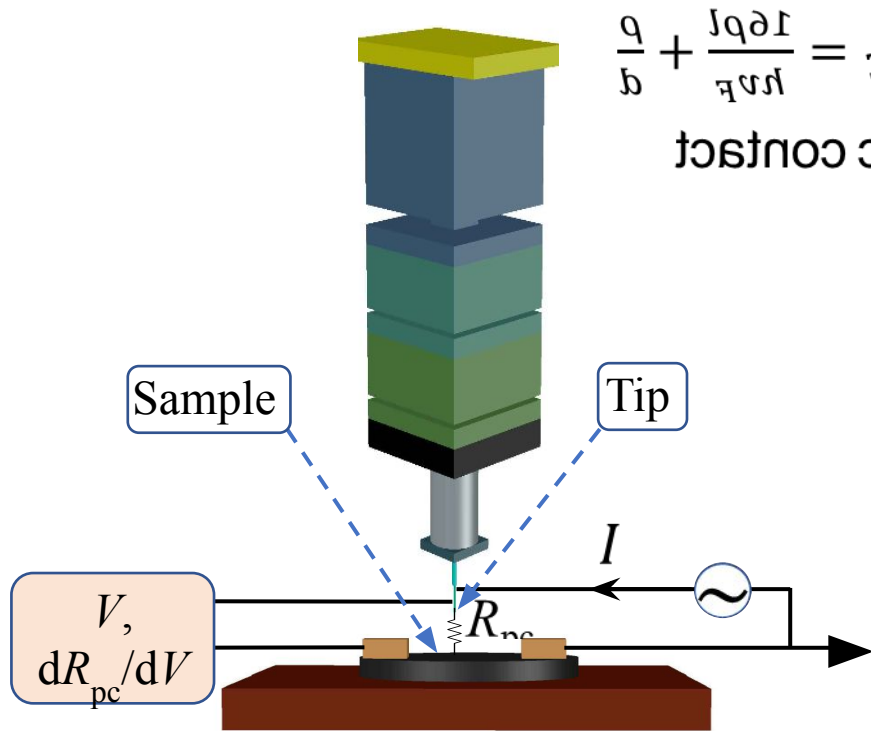
Two-channel transport

$$\frac{\Gamma}{\rho_{\parallel 0}} + \frac{\Gamma}{\rho_{\text{BG}}(T)} = \frac{\Gamma}{(\rho_{\parallel 0}) - (\rho_{\parallel}(T))}$$

$\rho_{\parallel} \sim \rho_{\text{MIR}}$



Point-contact spectroscopy – A primer



$$l \gg d_{pc}$$

Ballistic

$$\frac{1}{R_0} + \frac{1}{R_{pc}} = \frac{1}{R_{pc}}$$

Resistance at the point-contact: R_{pc}

$$\frac{1}{R_0} \frac{dR_{pc}}{dV} \approx \frac{8e^2}{3h^2} g(eV)$$

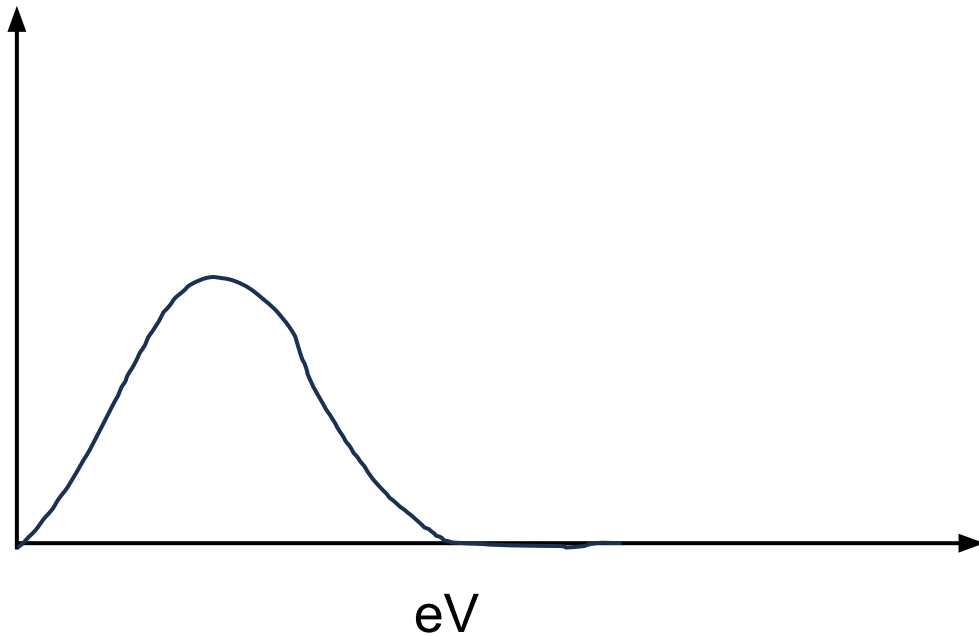
Ballistic contact

Migdal-Eliashberg function

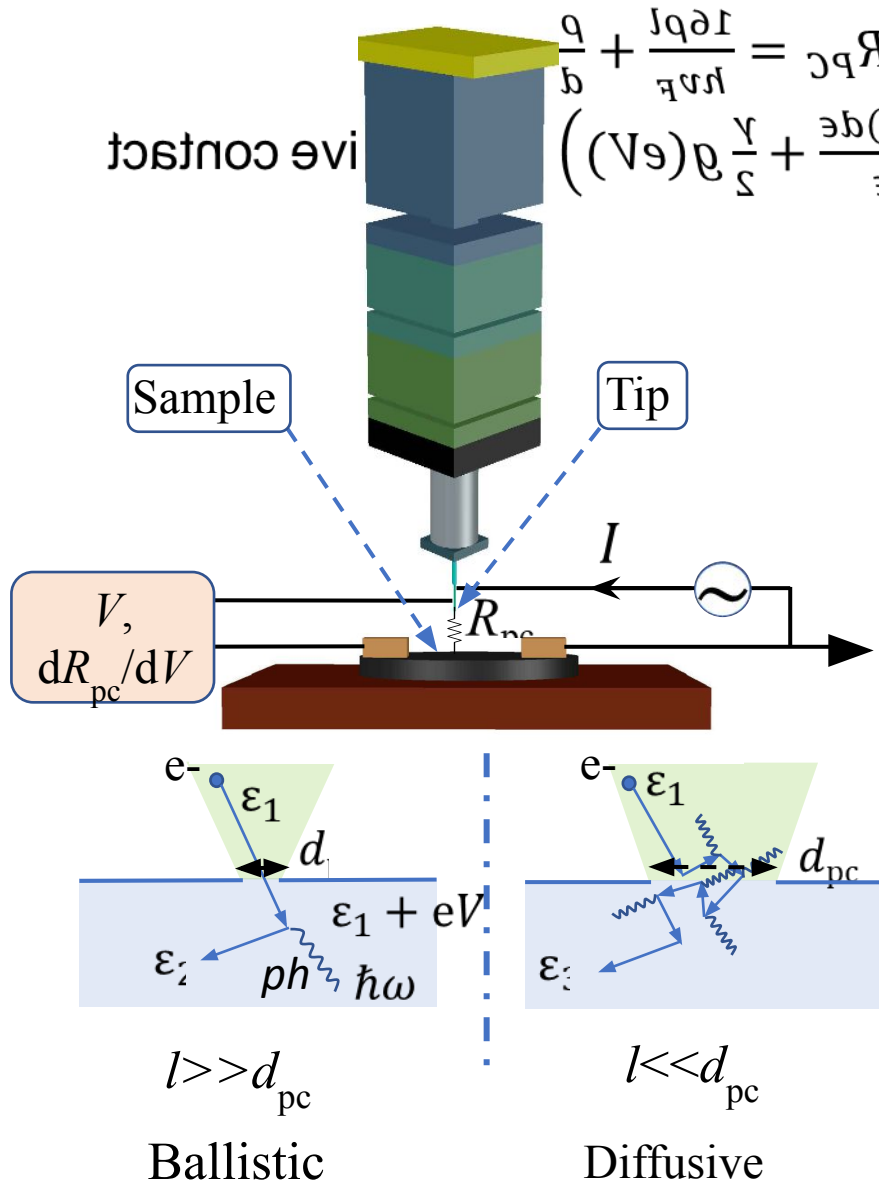
- Resembles Phonon DOS

$$\text{Electron phonon coupling constant: } \lambda = 2 \int_0^\infty \frac{g(\epsilon)}{\epsilon} d\epsilon$$

$$\frac{1}{R_0} \frac{dR_{PC}}{dV}$$



Point-contact spectroscopy – A primer



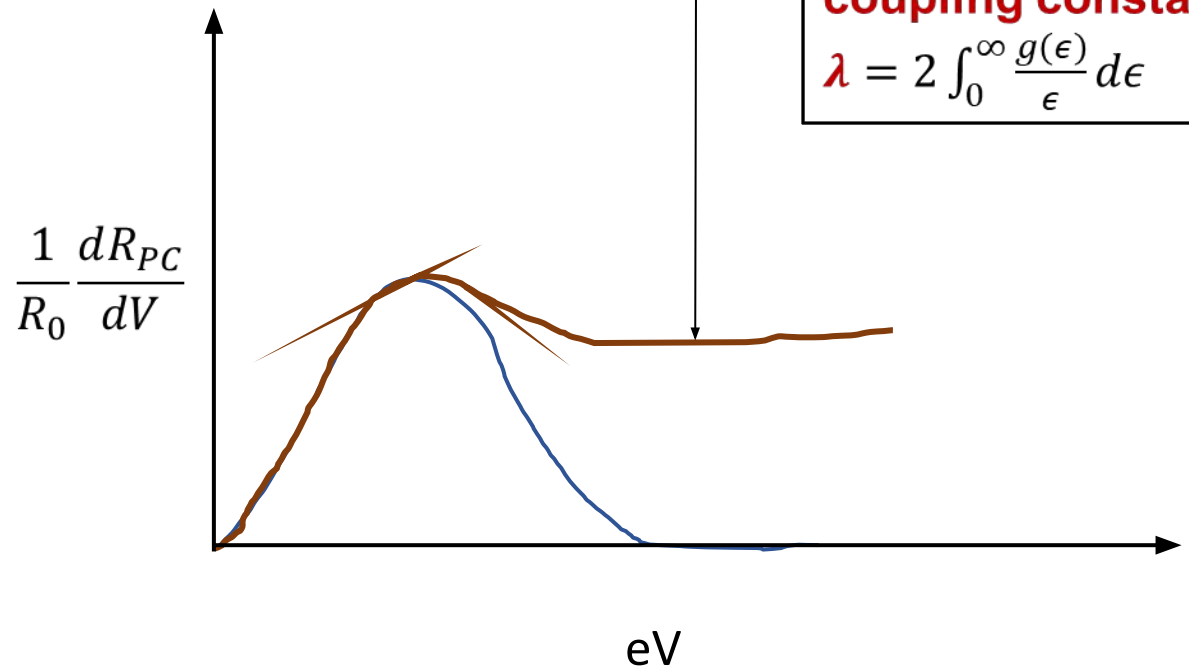
Resistance at the point-contact: $R_{pc} = \frac{R_0}{2} + \frac{1}{2} \int_0^{eV} g(\epsilon) d\epsilon + \gamma \int_0^{eV} \frac{g(\epsilon) d\epsilon}{\epsilon} + \frac{8e^2 R_{pc}}{3h^2 v_F} g(\epsilon) \approx \frac{1}{2} \frac{dR_{pc}}{dV} R_0$

Migdal-Eliashberg function Background

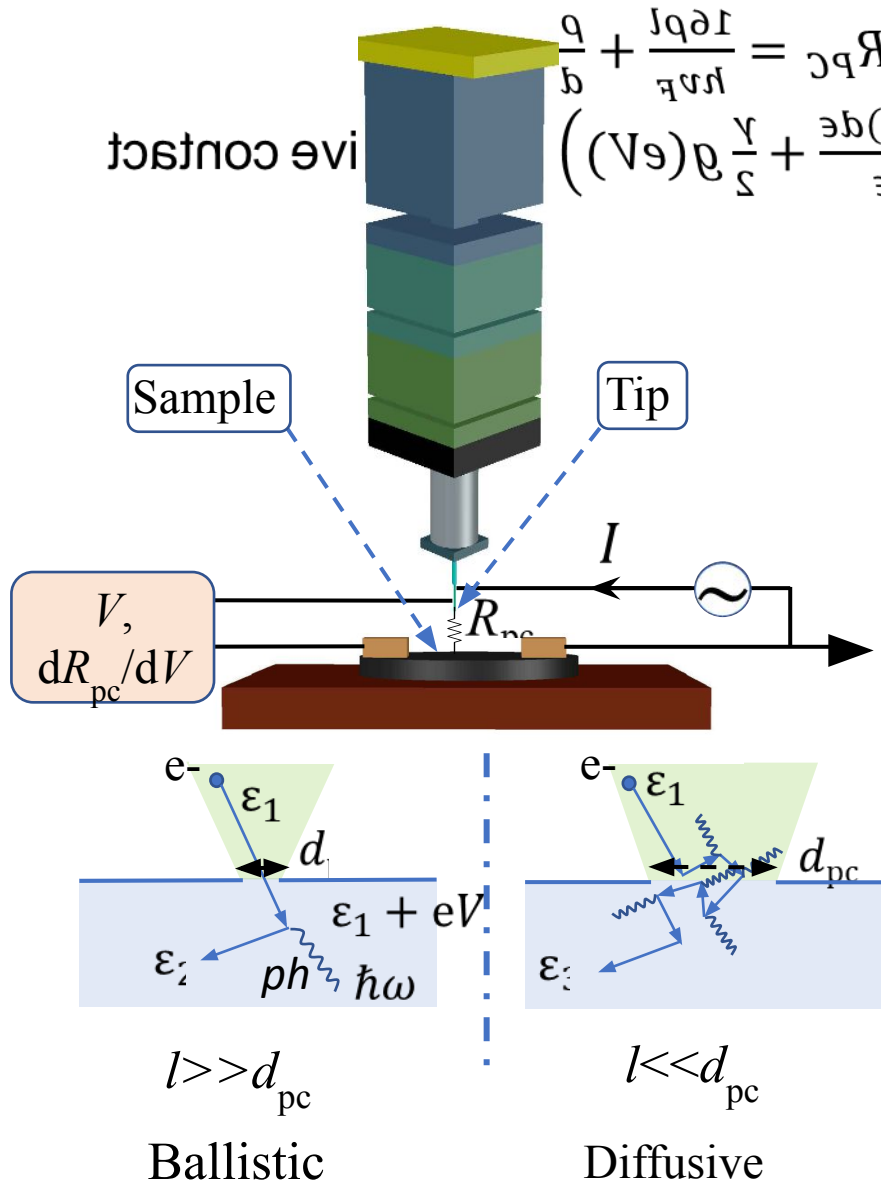
- Resembles Phonon DOS

Electron phonon coupling constant:

$$\lambda = 2 \int_0^\infty \frac{g(\epsilon)}{\epsilon} d\epsilon$$



Point-contact spectroscopy – A primer



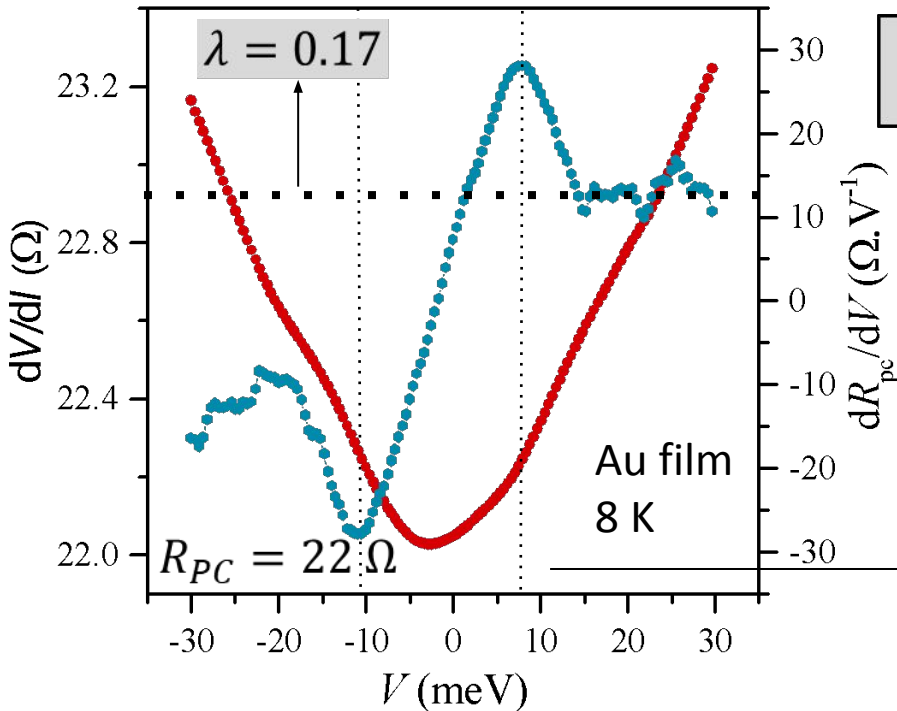
Resistance at the point-contact: $R_{pc} = \frac{R_0}{2} \left(\frac{1}{g(V)} + \frac{1}{g(V+eV)} \right) + \frac{1}{2} \int_0^{eV} g(\epsilon) d\epsilon$

Background: $\frac{1}{R_0} \frac{dR_{pc}}{dV} \approx \frac{2}{3} \frac{g(V)}{g(V+eV)}$

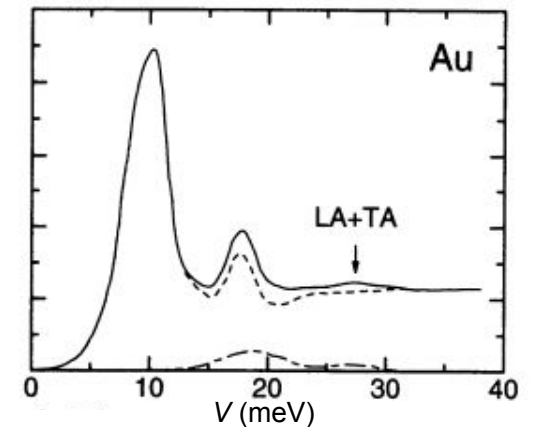
Migdal-Eliashberg function Background

- Resembles Phonon DOS

Electron phonon coupling constant: $\lambda = 2 \int_0^\infty \frac{g(\epsilon)}{\epsilon} d\epsilon$

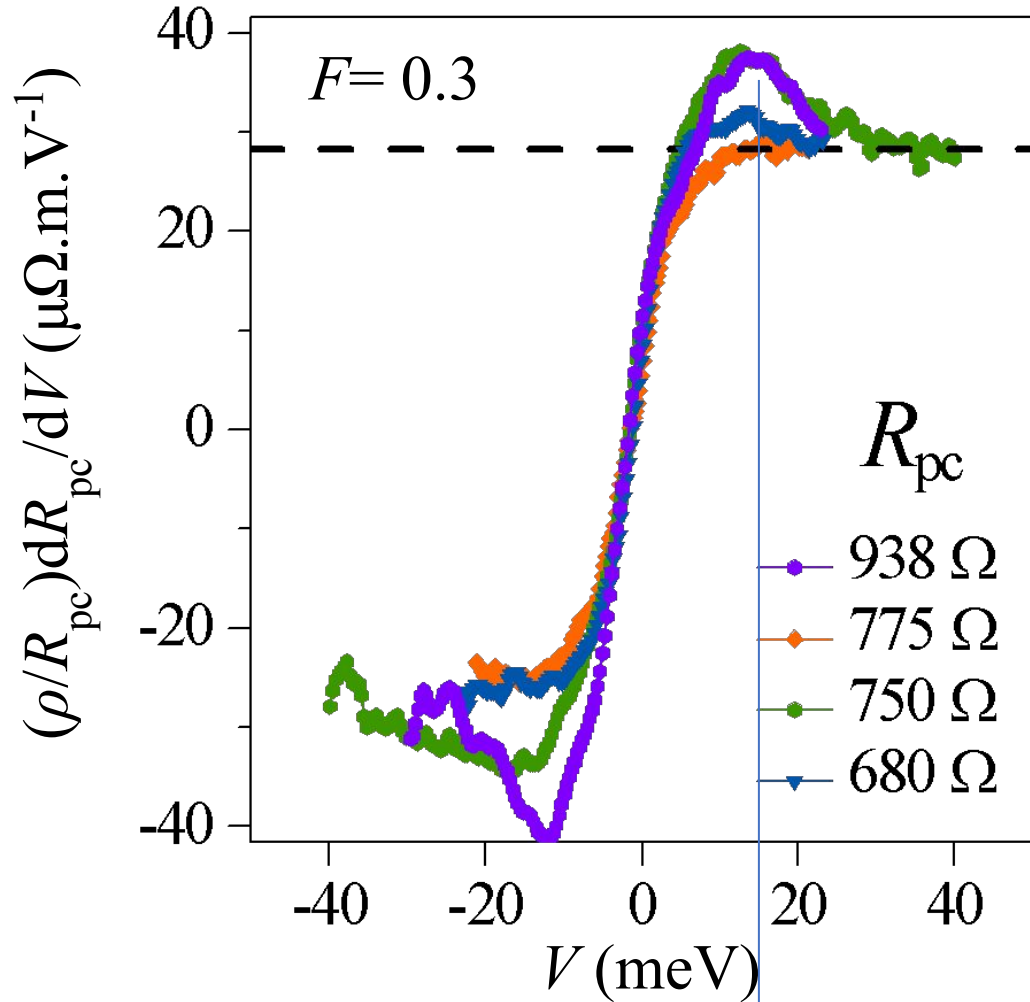


$\lambda = (\text{Const}) \times \frac{dR_{pc}}{dV} (eV \gg \hbar\omega_D)$

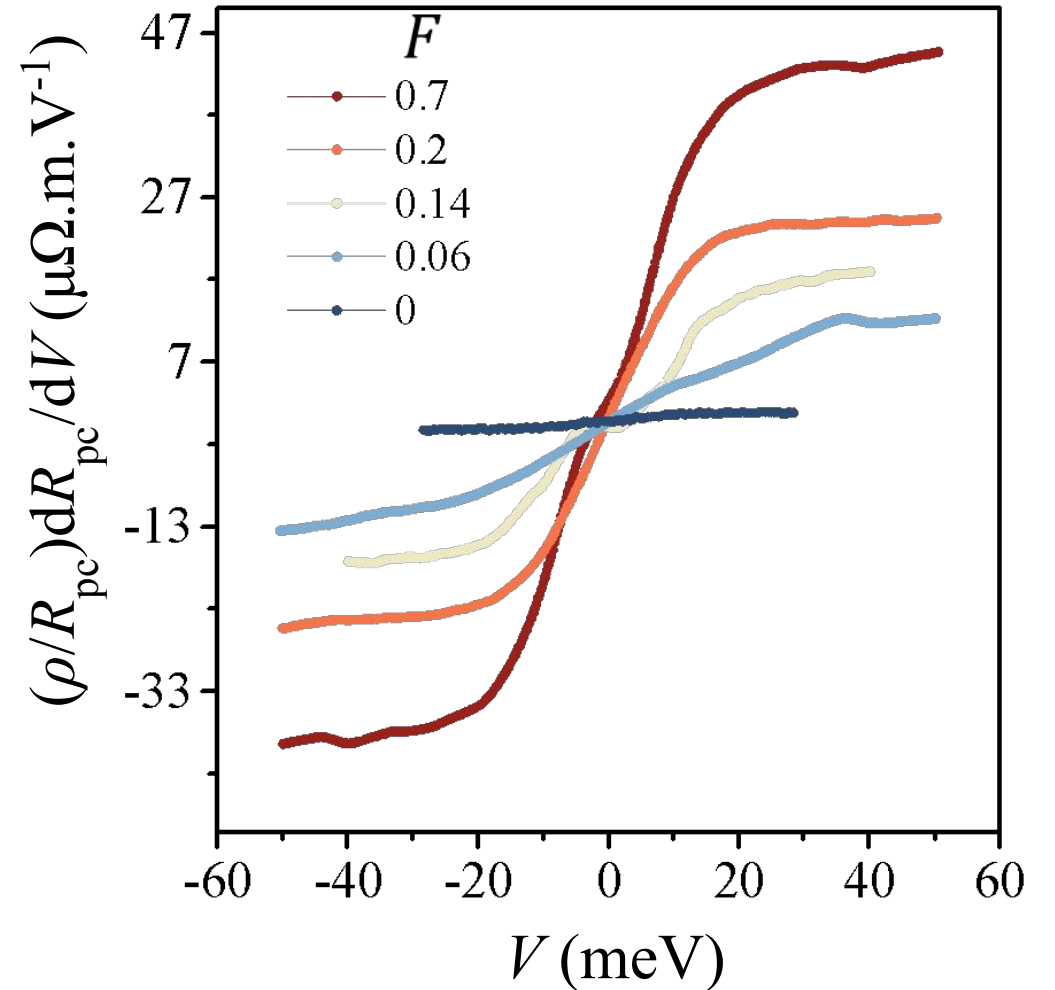


Point contact spectroscopy of nanohybrid films

$$\lambda = \frac{3\pi n e h}{16m} d_{pc} \times \frac{dR_{pc}}{dV} (eV \gg h\omega_D)$$

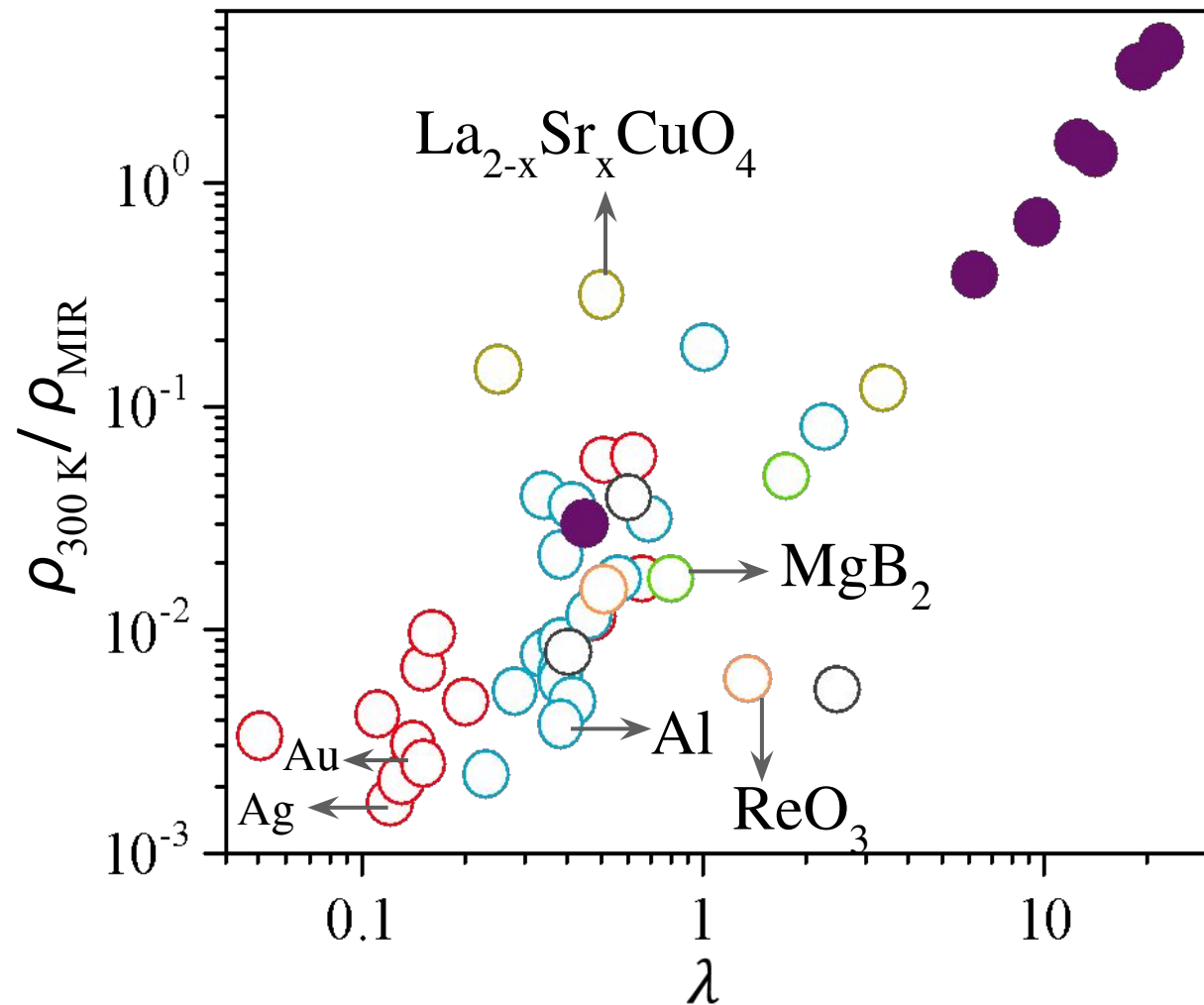
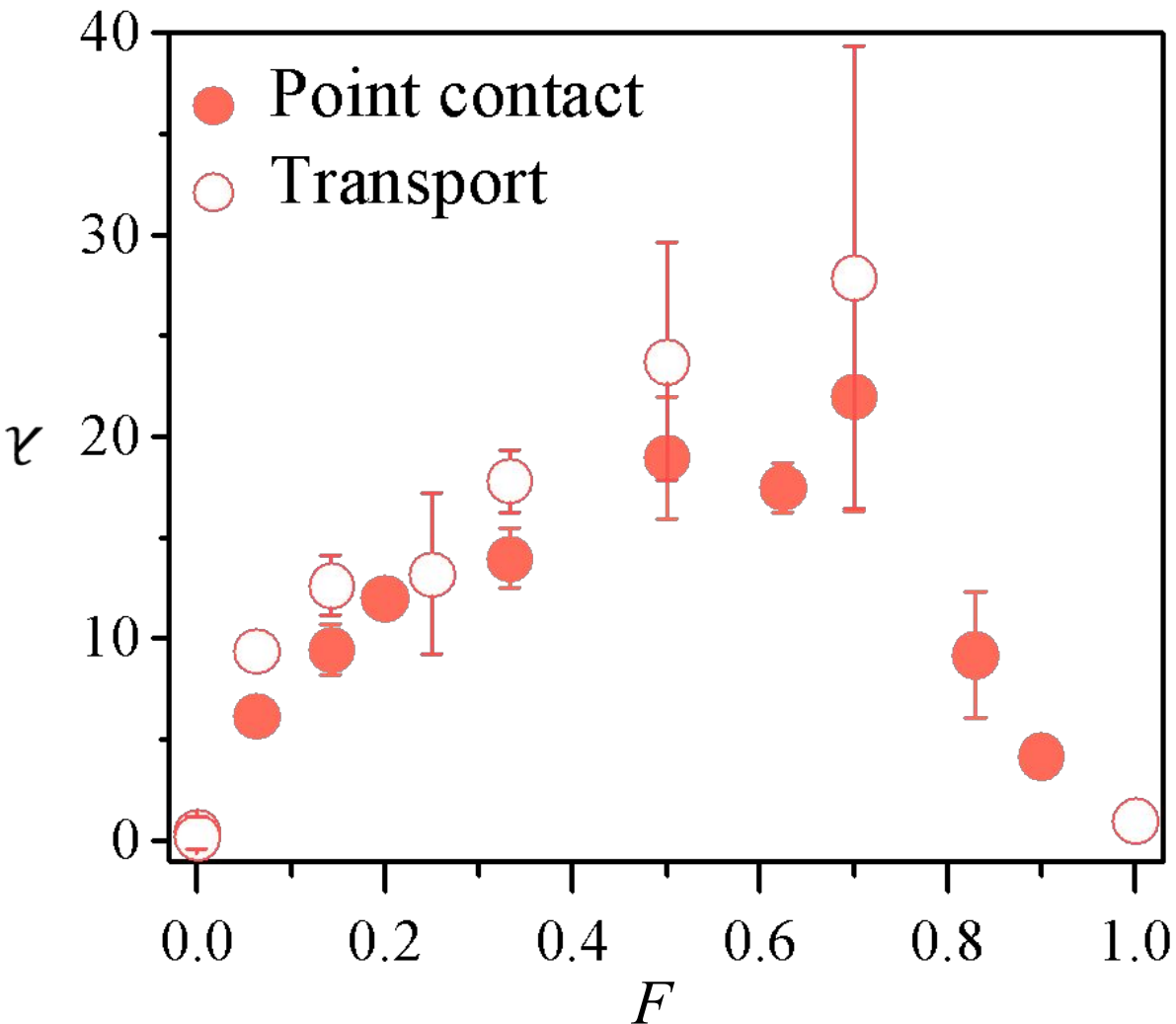


- Saturation of the spectra at ~ 18 meV
Acoustic phonons of Au



- Increasing background with F

Electron-phonon coupling in metallic nanohybrid films

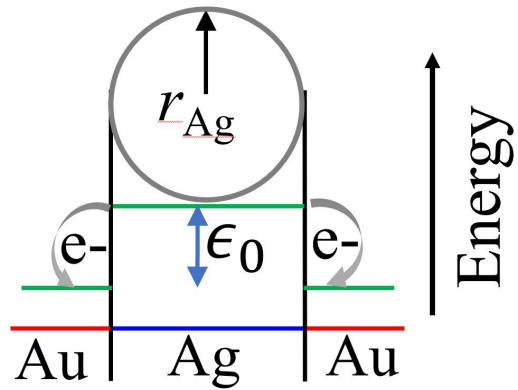


□ Significant increase in with F

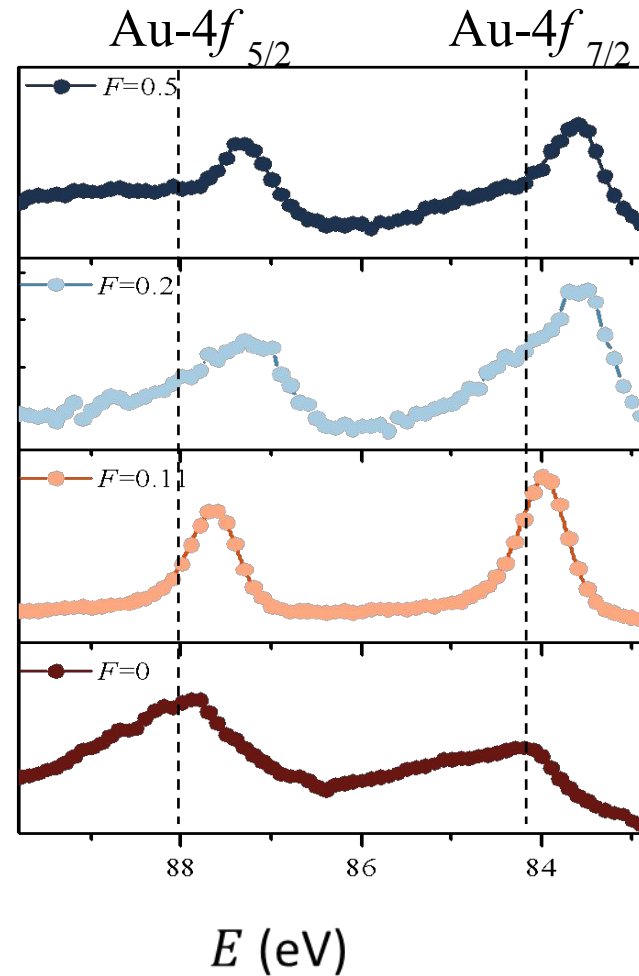
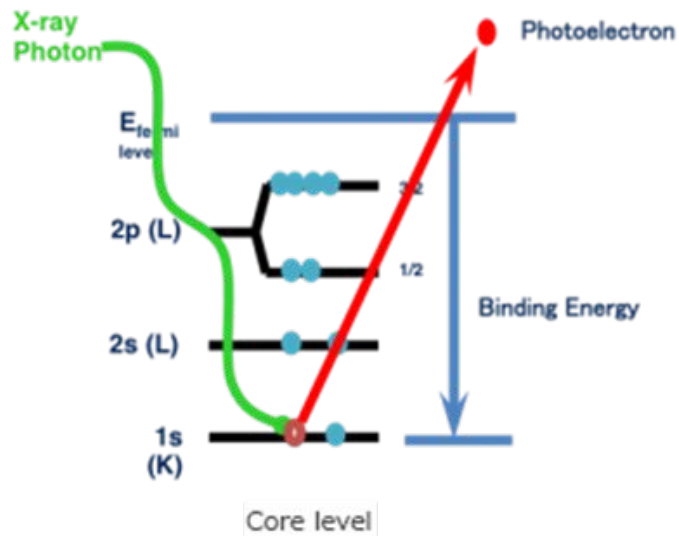
University of Cambridge
 dominates high T resistivity in a wide class of materials
 $\propto \lambda$, Electron-phonon coupling

• [arXiv:2405.14684v1](https://arxiv.org/abs/2405.14684v1)

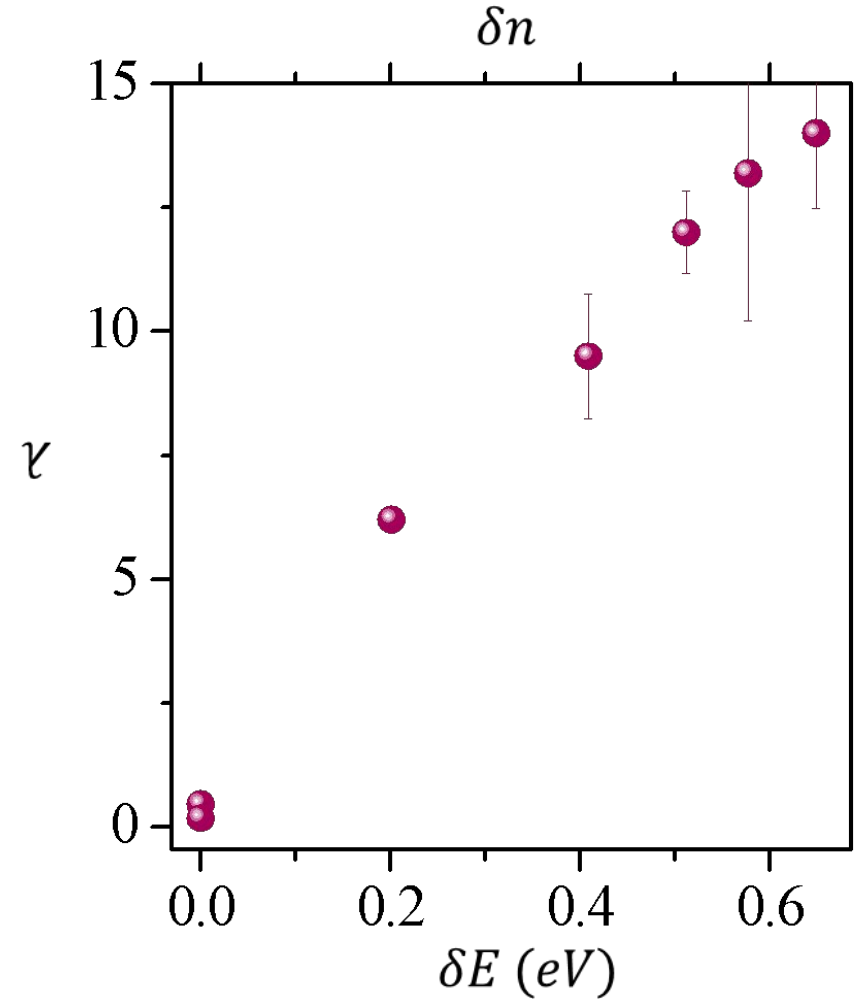
Role of nanoscale interfaces



Charge doping from difference in onsite potential



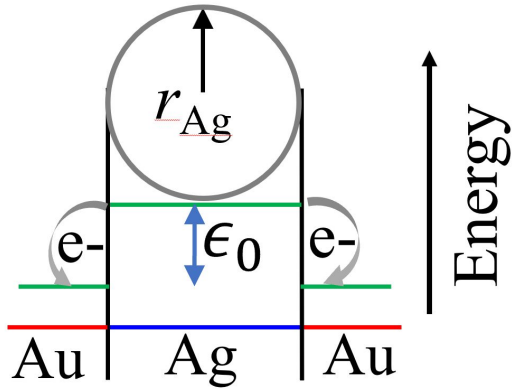
Shift in Au 4f peak in XPS
Charge doping



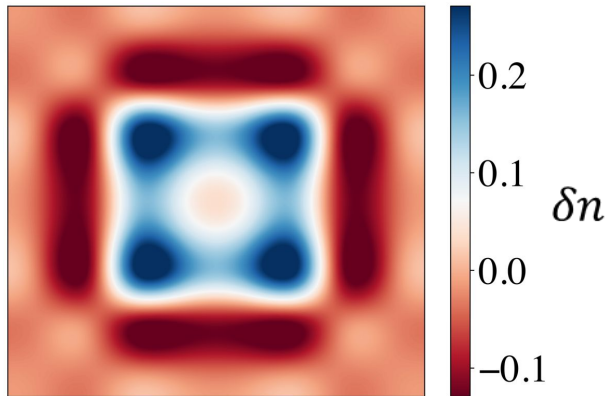
Variation of EPC with interfacial charge transfer

- Possible role of Coulomb interactions

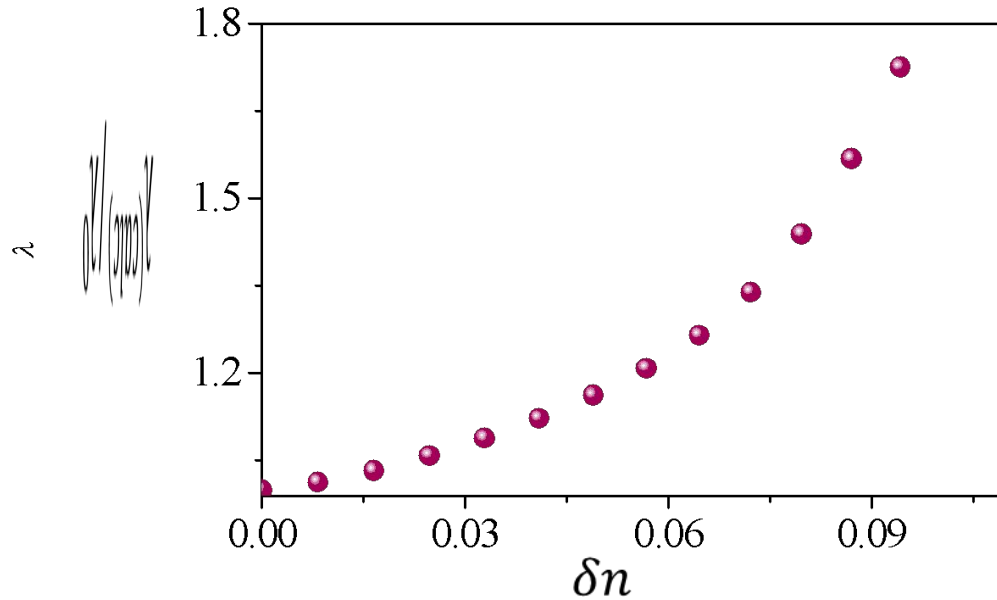
Role of nanoscale interfaces: Theoretical insight



Charge doping from difference in onsite potential



Charge distribution in a square lattice:
4 × 4 Ag sites surrounded by 8 × 8 Au sites



➤ Contributions to the electron-phonon matrix elements from Coulomb interactions of electrons to interfacial charge

$$g_{ce} \propto V_0(\delta n)$$

V_0 : Inter-site Coulomb repulsion

- [arXiv:2405.14684v1](https://arxiv.org/abs/2405.14684v1)
- Details coming out in another paper soon



Shinjan Mandal



Manish Jain



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Summary

- Bottom-up metal-nanocomposite
- Unconventional metallic transport: Bad metals
- Buried interfaces of Ag and Au significantly enhance the electron-phonon coupling in noble metals, which have intrinsically the weakest coupling

Questions?

- Origin of high values of EPC
- Existence of metallic state in strong EPC regime
- No crossover to Anderson insulator even for strong disorder
- Possible coexistence of localized and itinerant electrons?

*Stay tuned for **Arindam's talk on 26th July** for more details and results!*

Thank you for your attention

EXTRA SLIDES

Scaling of electron-phonon scattering rate

Ignore any non-phonon temperature-dependent scattering

$$\rho(T) = \rho_0 + \rho_{e-ph}(T)$$

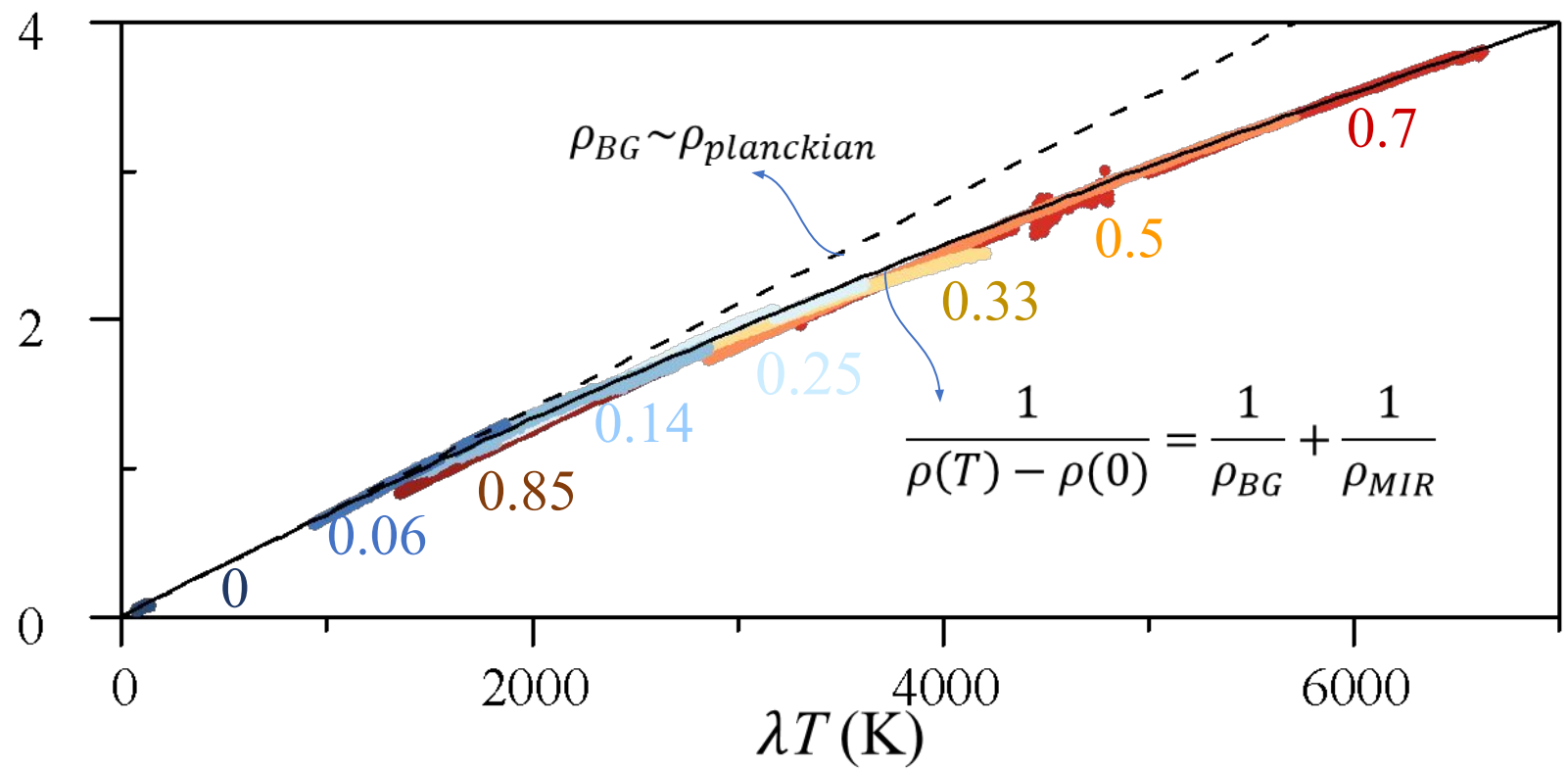
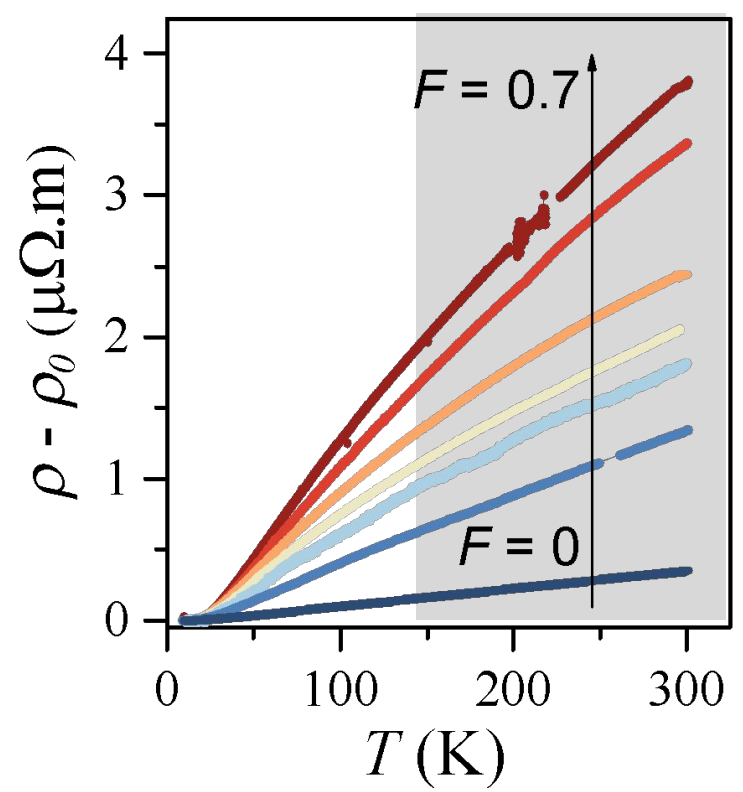
Disorder

$T > \Theta_D$

$$\rho_{e-ph} = \frac{m}{ne^2\tau_{e-ph}}, \tau_{e-ph}^{-1}(T) = \left(\frac{2\pi k_B}{\hbar}\right) \times (\lambda T)$$

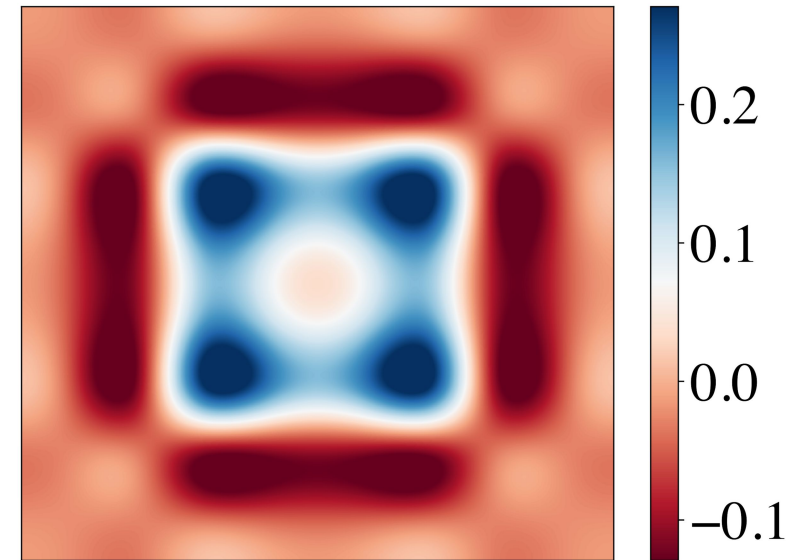
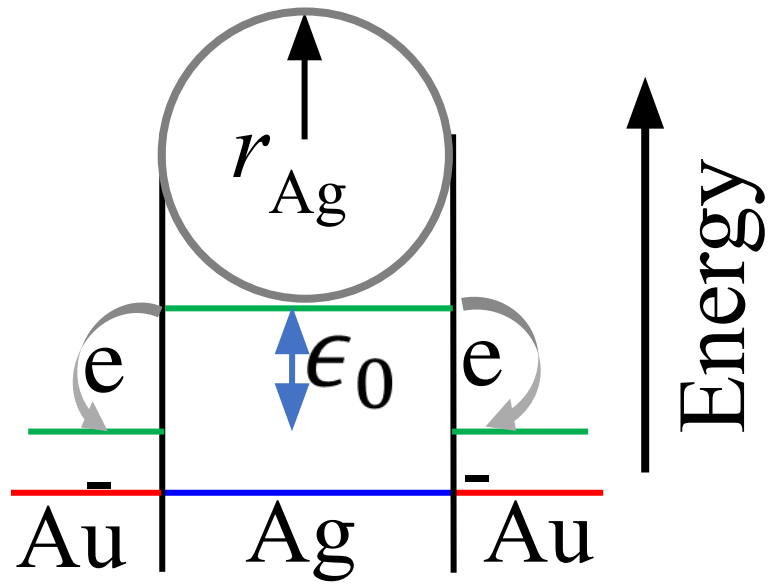
Planckian bound

Point contact

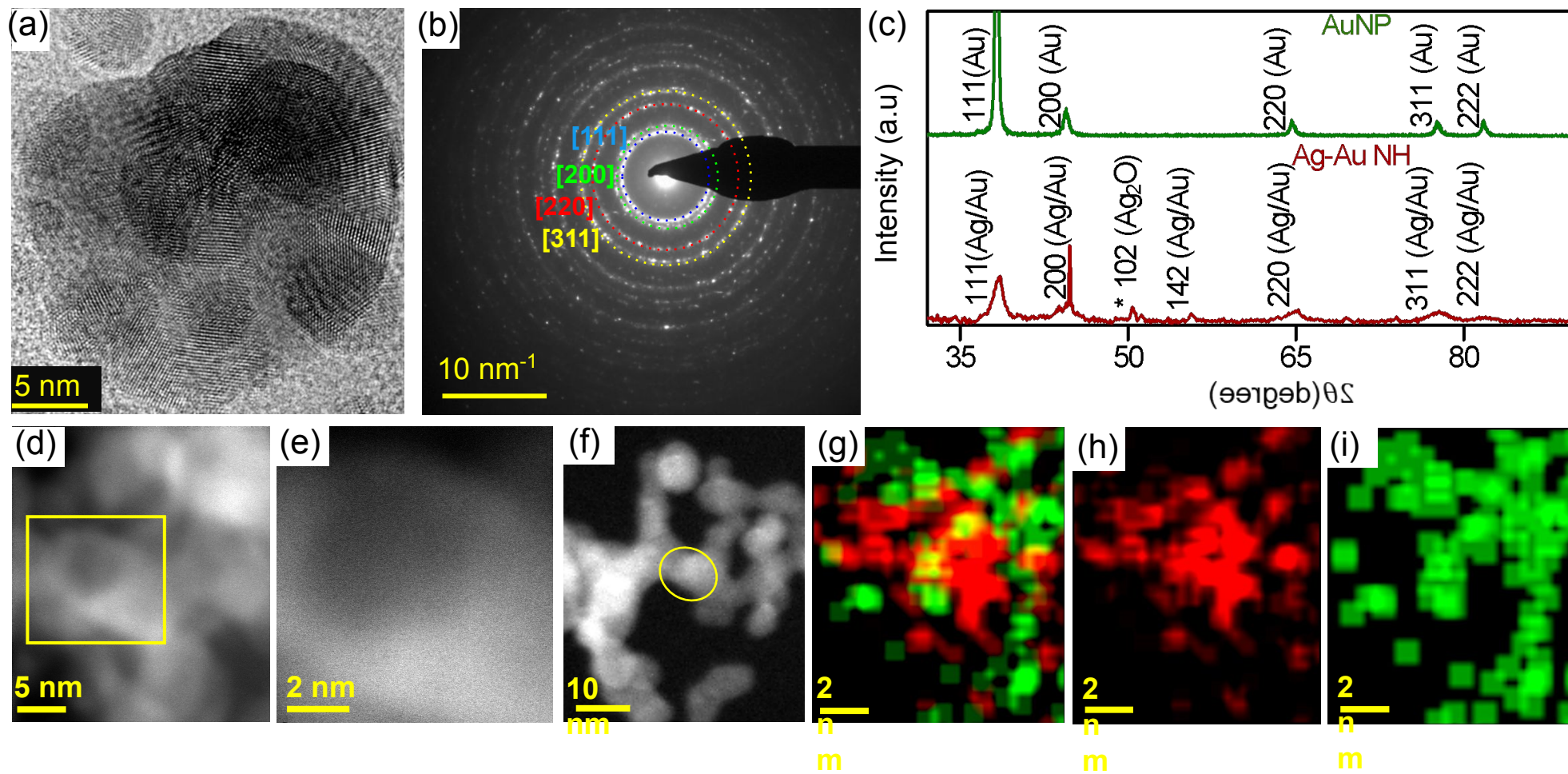


- Bound in scattering rate at ultra-high coupling regimes
- Universality of a two-channel transport

Role of nanoscale interfaces



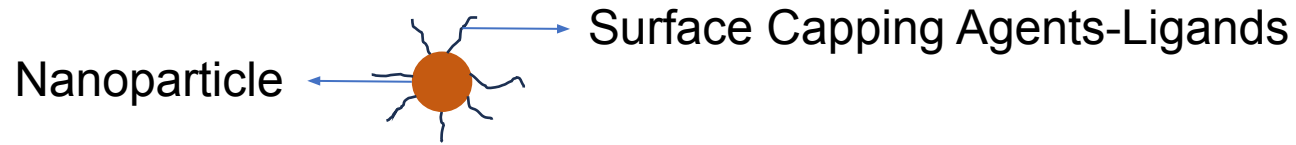
Structure



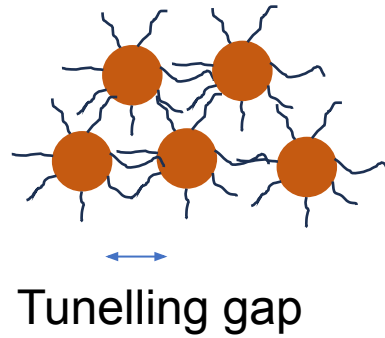
Motivation

Not achieved: Bottom-up assembly of 'Metal' with nanoparticles

Electron tunneling effects: Coulomb blockade, Variable Range hopping, Activated transport



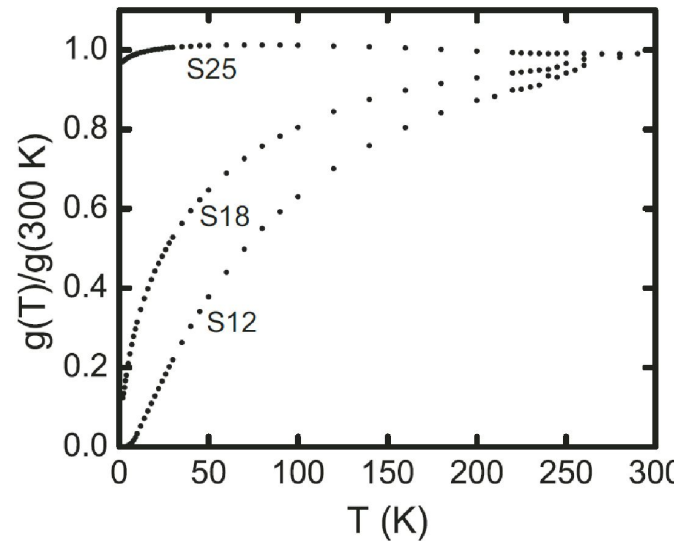
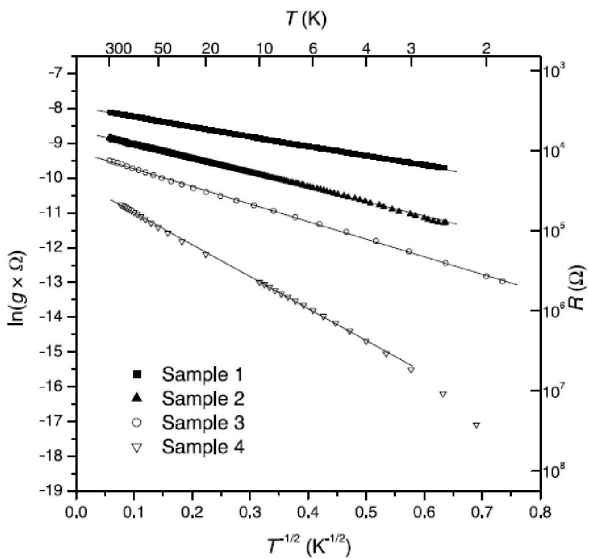
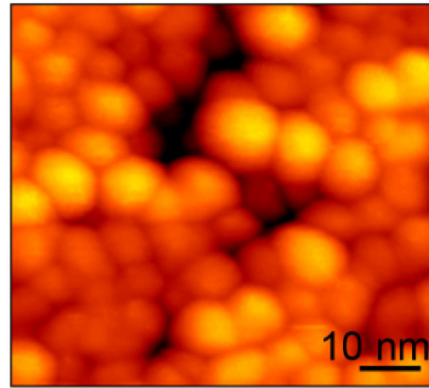
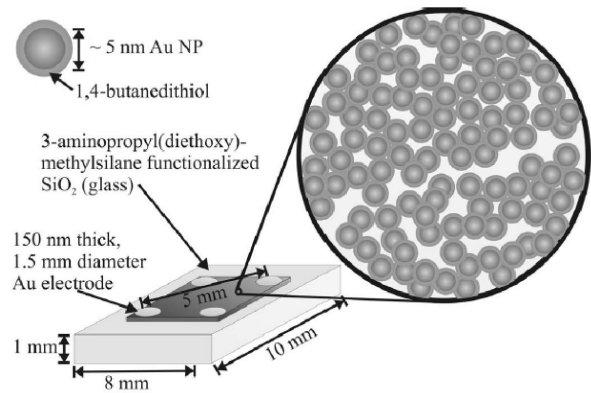
Assembly of nanoparticles



Motivation

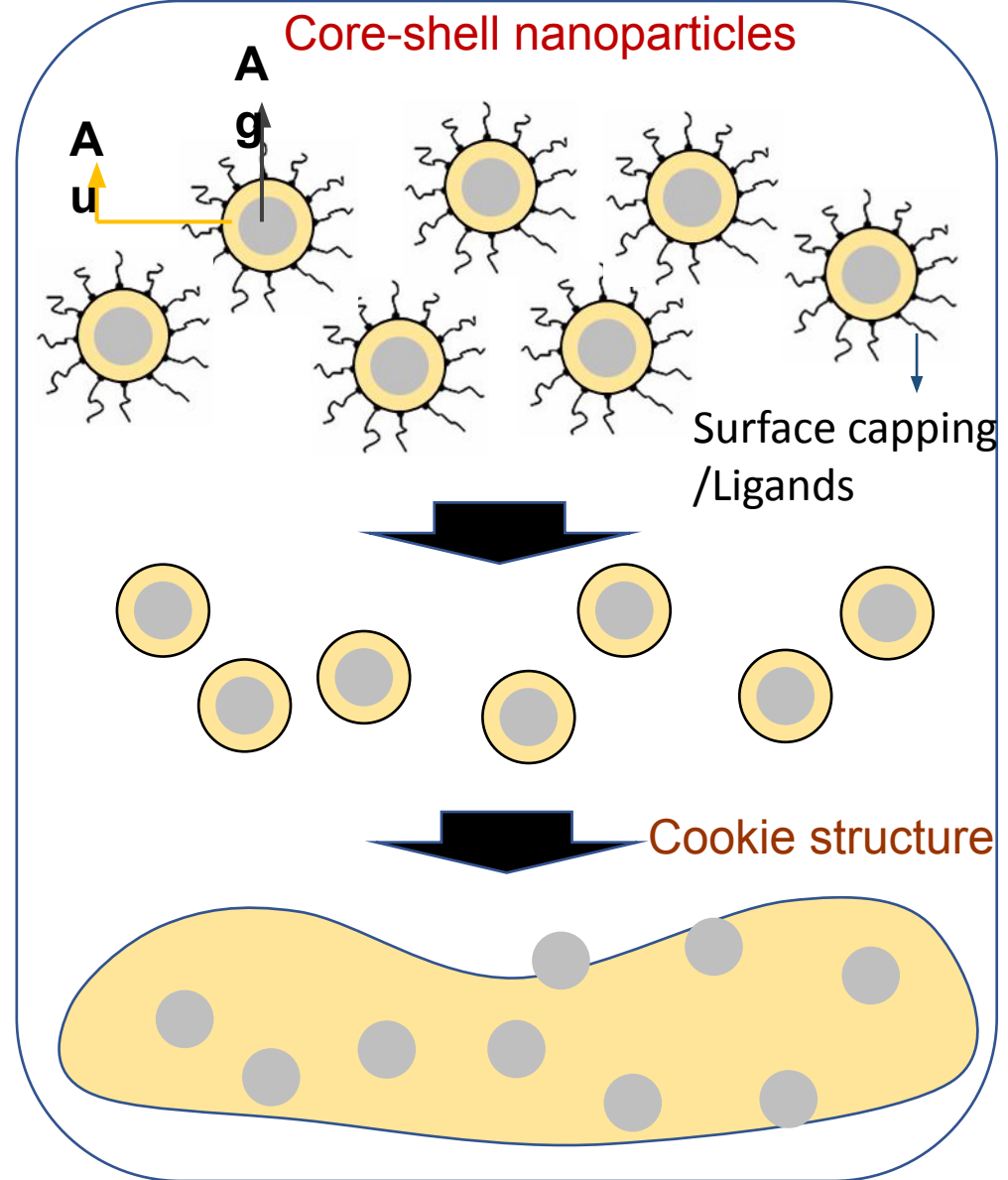
Not achieved: Bottom-up assembly of 'Metal' with nanoparticles

Electron tunneling effects: Coulomb blockade, Variable Range hopping, Activated transport



A bi-metallic nano-hybrid

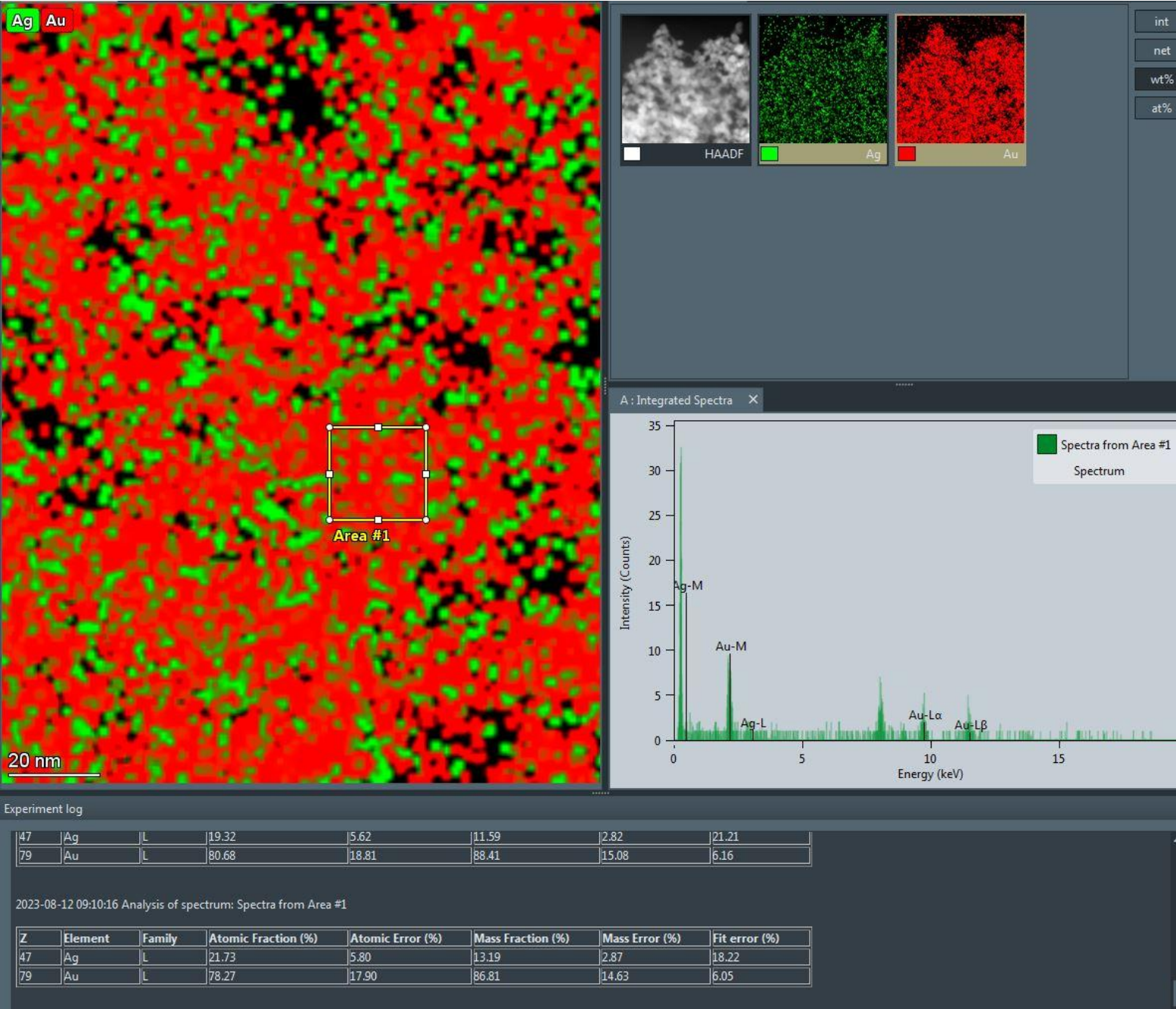
Core-shell nanoparticles

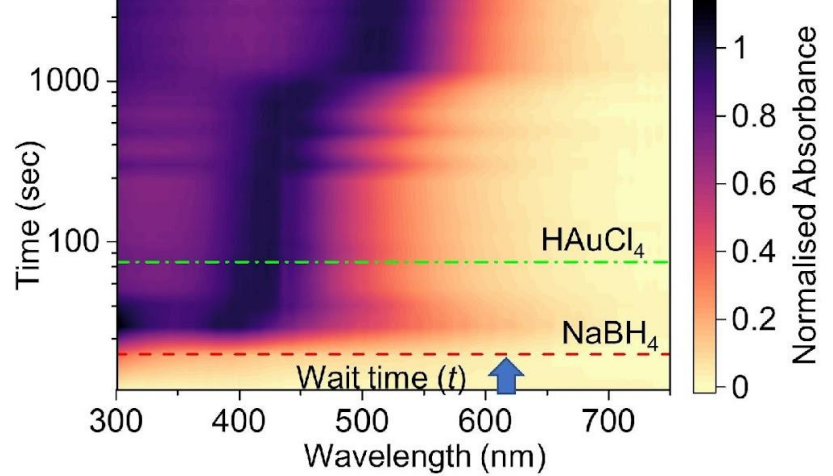
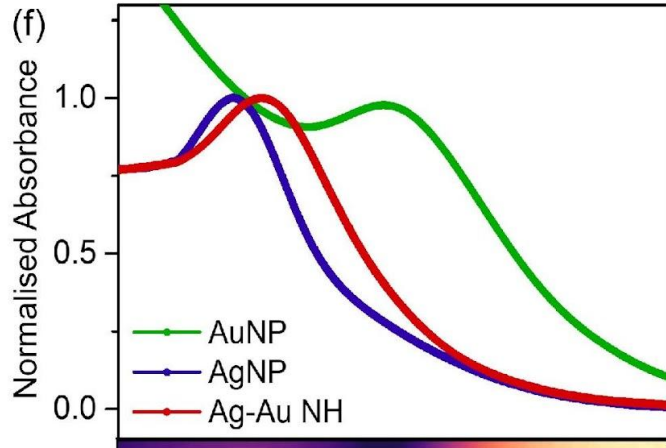
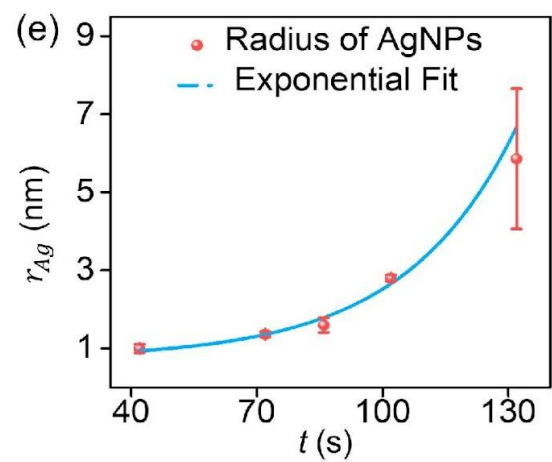
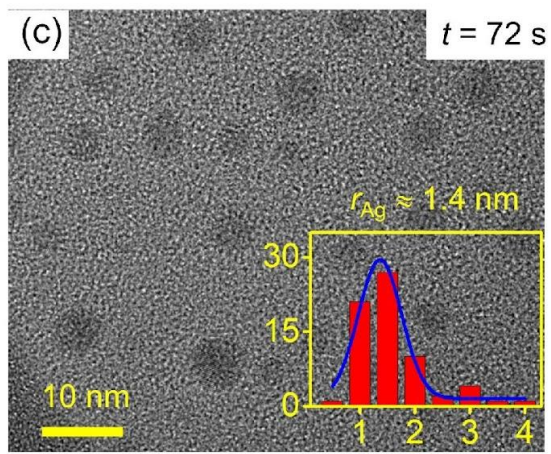
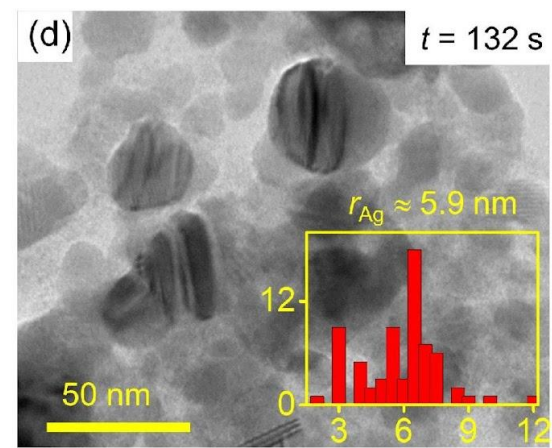
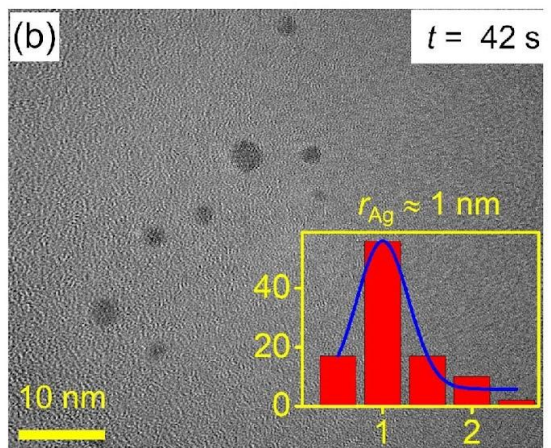
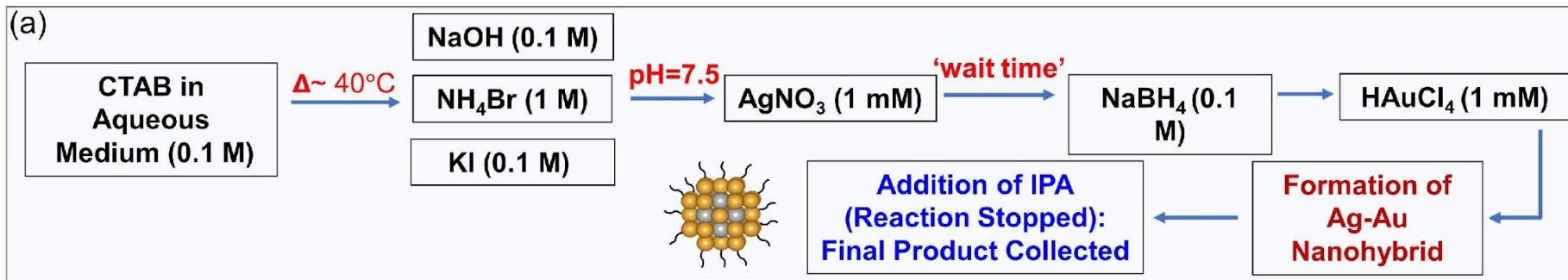


Surface capping /Ligands

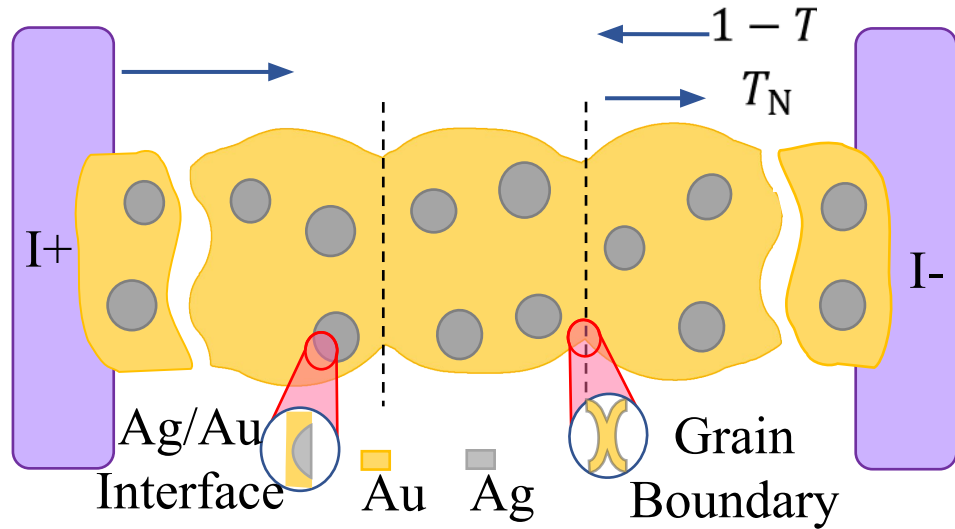
Cookie structure

Structure





Resistivity – interface correlation



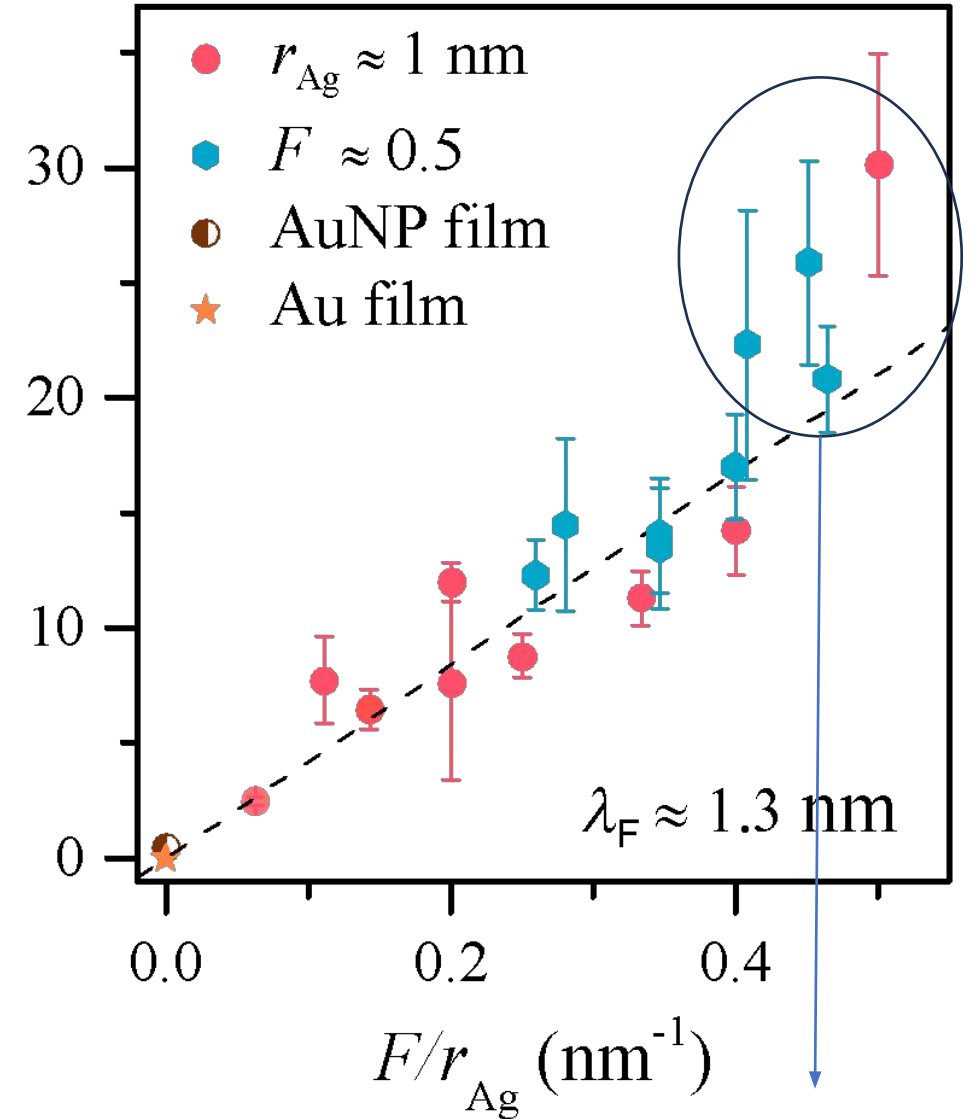
➤ Interface of AgNPs as dominant scatterers

☐ Mean free path : $\lambda = \frac{1}{\sigma n}$

☐ Landauer-Buttiker formalism :

$$R = \frac{h}{e^2} \frac{(1-T_N)}{MT_N}, T_N = \frac{\lambda}{L+\lambda}, M : \text{no. of modes} = \frac{L^2}{\lambda_F^2}$$

$$\rho_0 = \frac{h}{e^2} \frac{\lambda_F^2}{r_{Ag}} \frac{f}{1+f}$$



Resistivity approaching the Mott-Ioffe-Regel limit!

Resistivity saturation

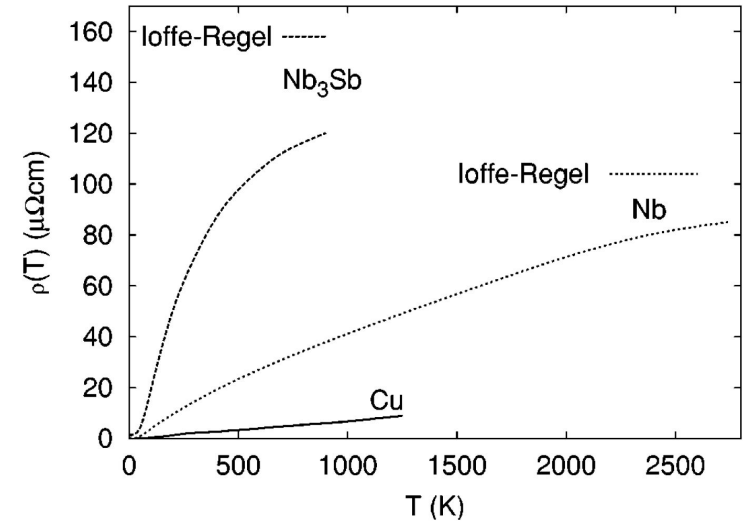
The Mott-Ioffe-Regel (MIR) Limit and 'bad metals'

$$\frac{v_A v}{v_A v + v_A v} = 1$$

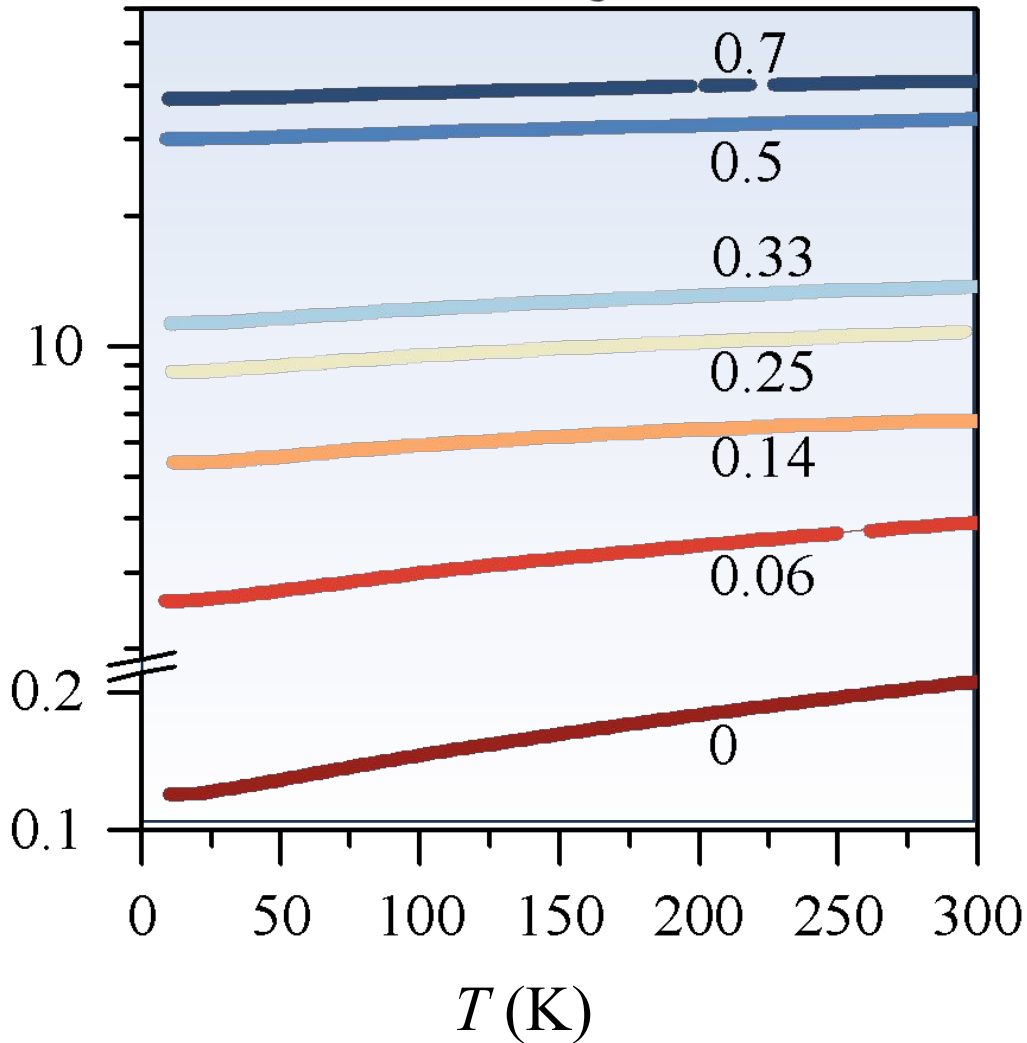
MIR Limit: $k_F l = 1$ $\rho_{MIR}^{Au} = 24.6 \mu\Omega\text{-m}$

$$\frac{\hbar^2 \pi \epsilon}{e^2 k_F} = \frac{\hbar^2 \pi \epsilon}{(j_F k_F) e^2 k_F} = \rho_{MIR}$$

- Mean-free path approaching inter-atomic distance
- Ill-defined quasiparticles

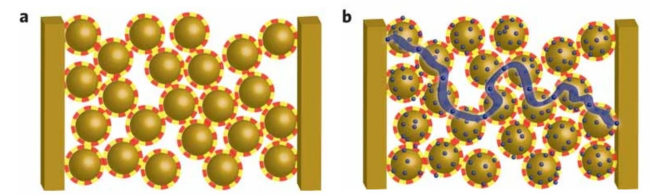
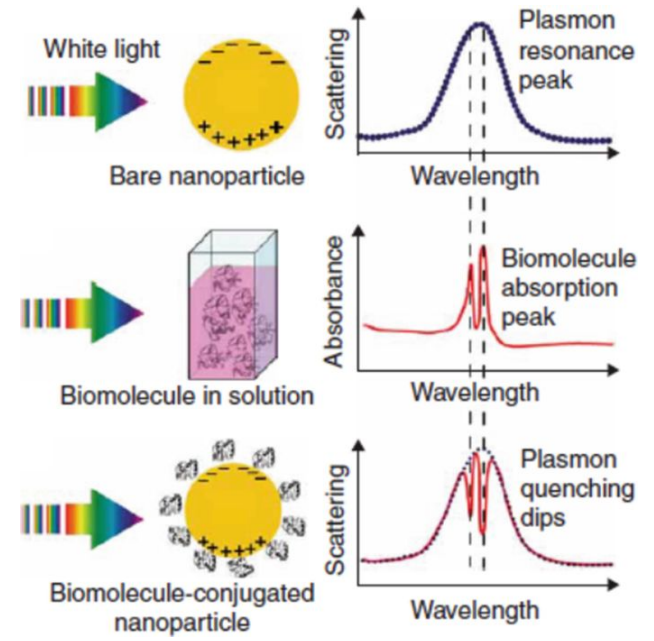
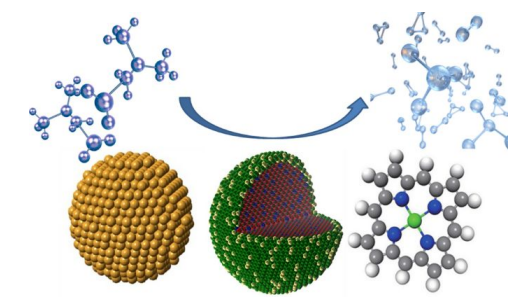
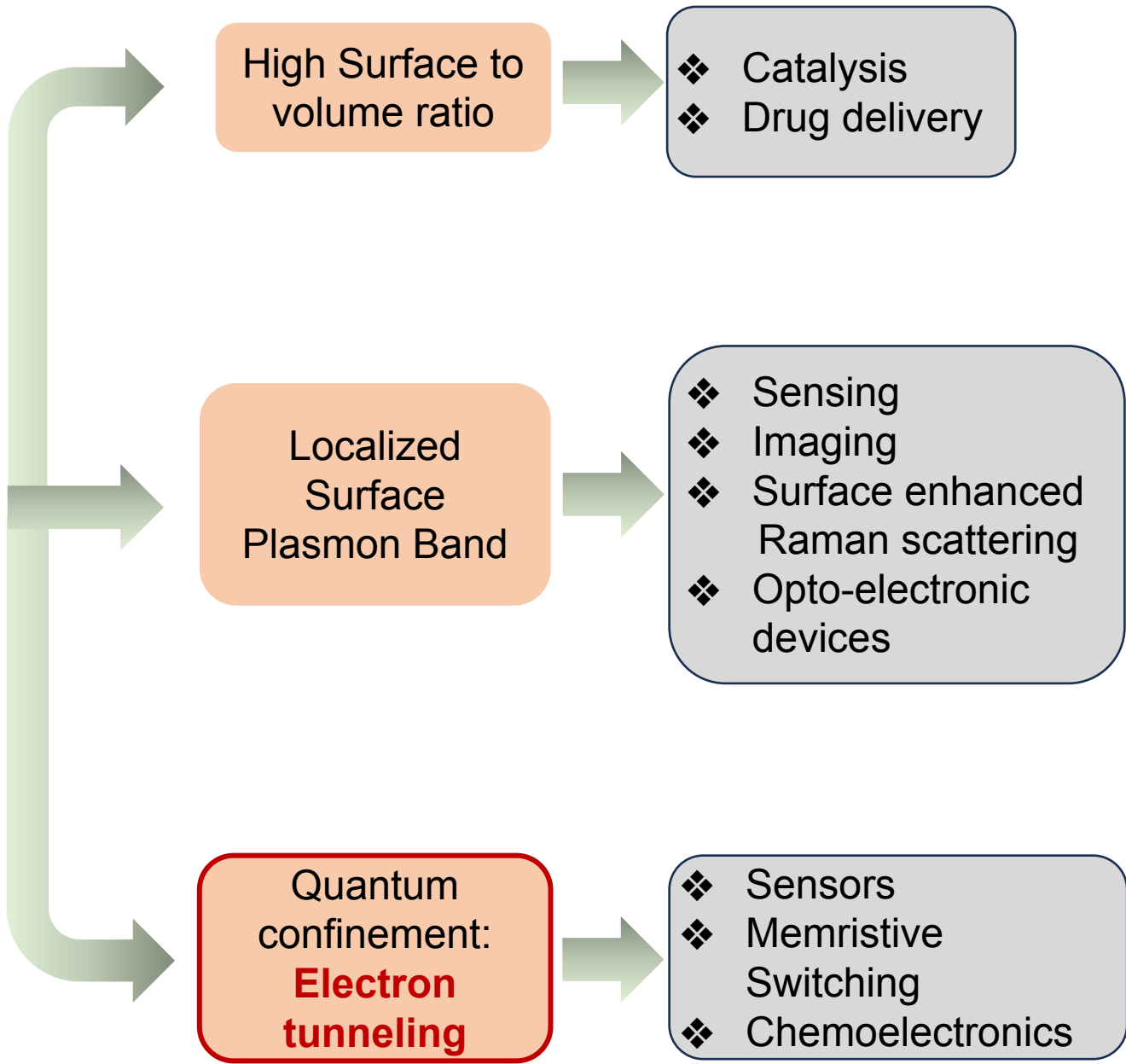
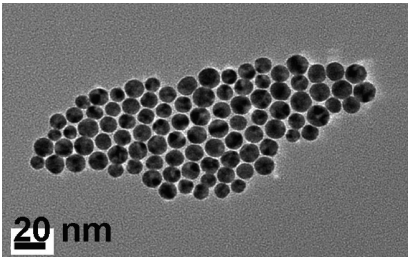


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Metal Nanoparticles-A primer:

Nanoparticles
➤ Metal Nanoparticles
~1 – 100 nm



Change in tunnelling current for sensing applications

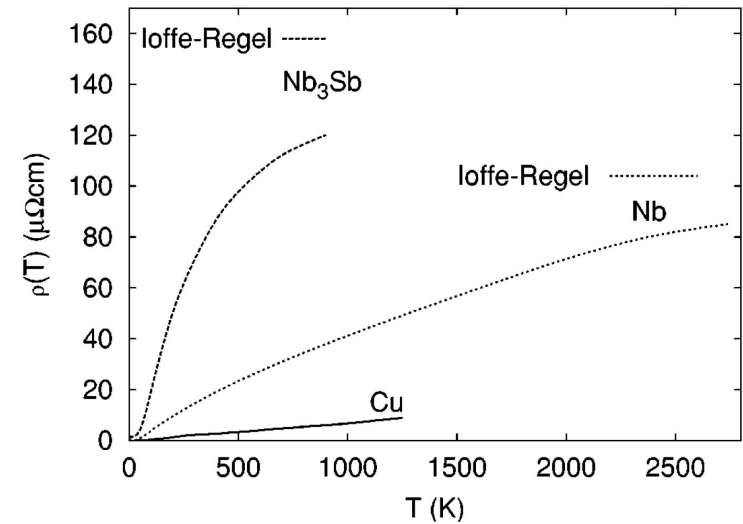
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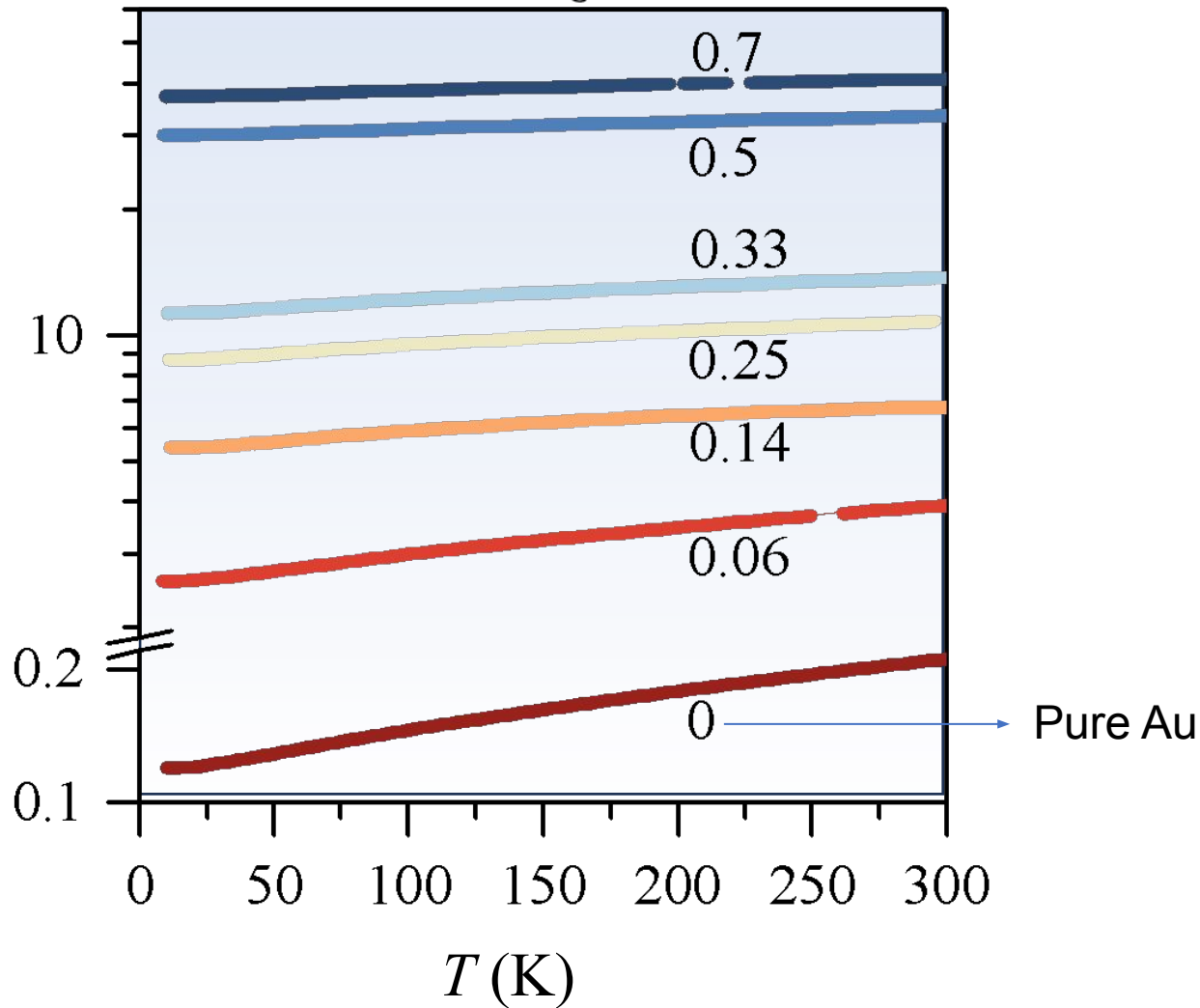
MIR Limit: $k_F l = 1$ $\rho_{MIR}^{Au} = 24.6 \mu\Omega\text{-m}$

$$\frac{\hbar^2 \pi \epsilon}{e^2 k_F} = \frac{\hbar^2 \pi \epsilon}{(J_F k_F) e^2 k_F} = \rho_{MIR}$$

- Mean-free path approaching inter-atomic distance
- Ill-defined quasiparticles

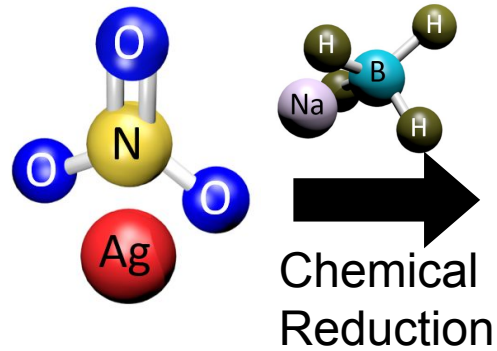


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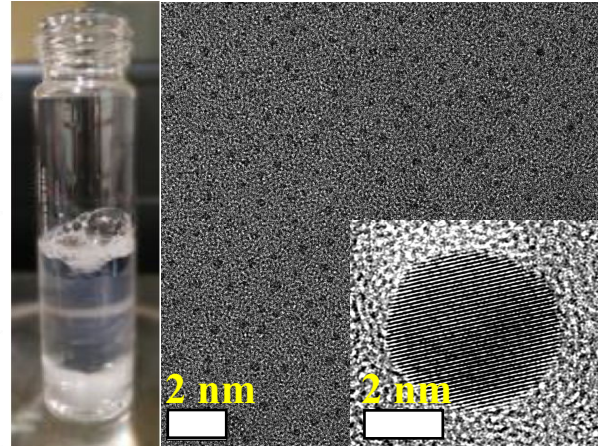


Chemical route – The process flow

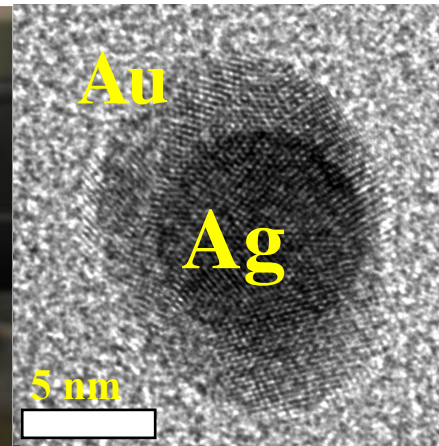
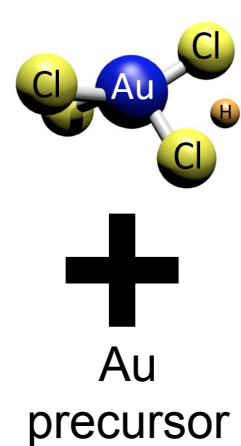
Ag(NP) – Au hybrid



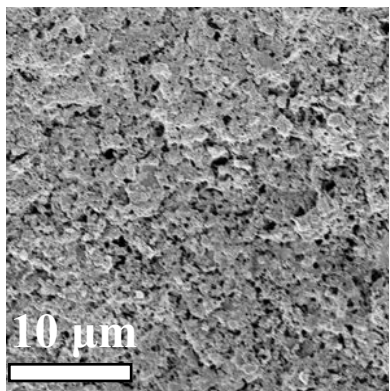
Ag precursor



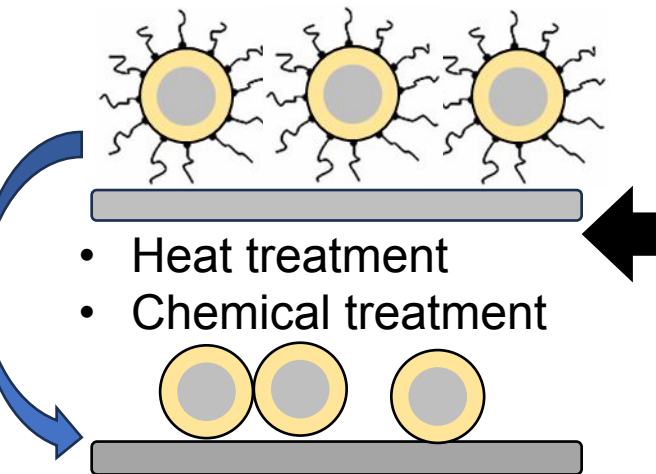
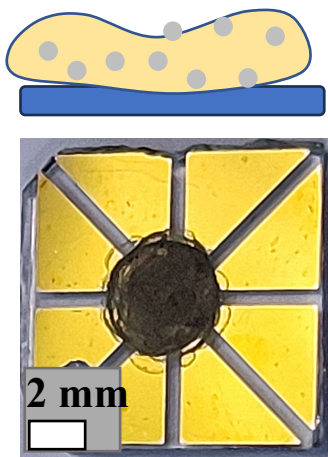
Ag nanoparticles



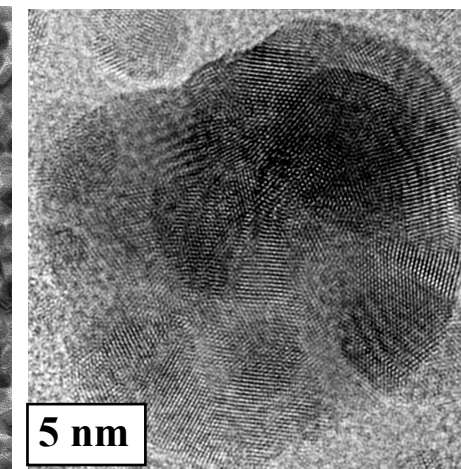
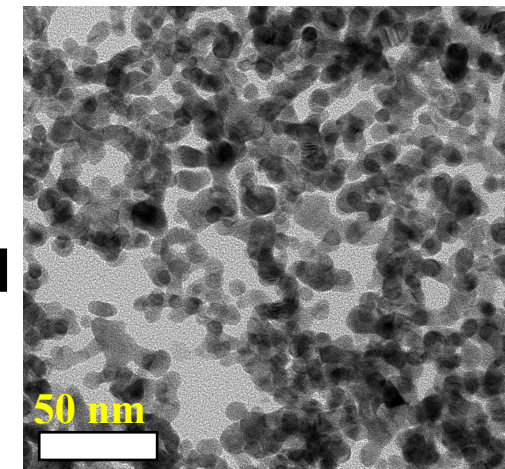
Ag@Au nanohybrid



Film for transport measurements



Ligand removal and cross-linking

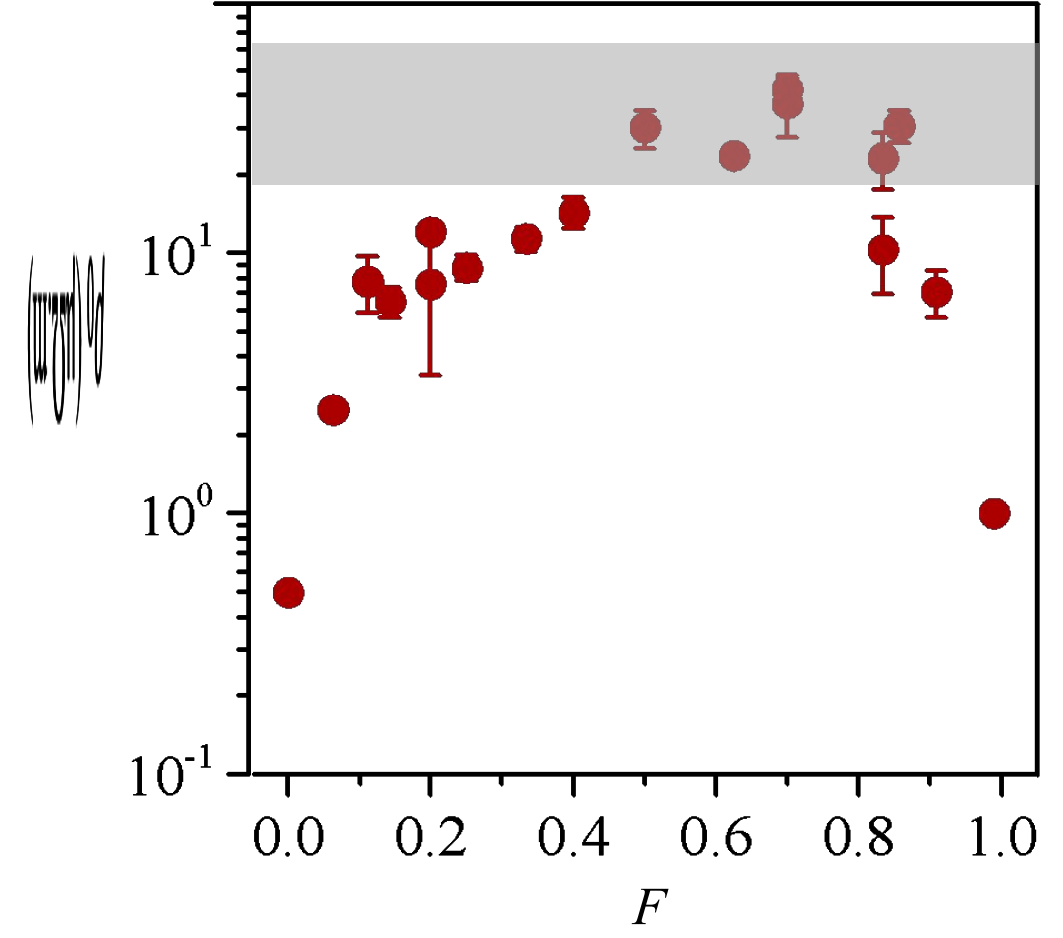
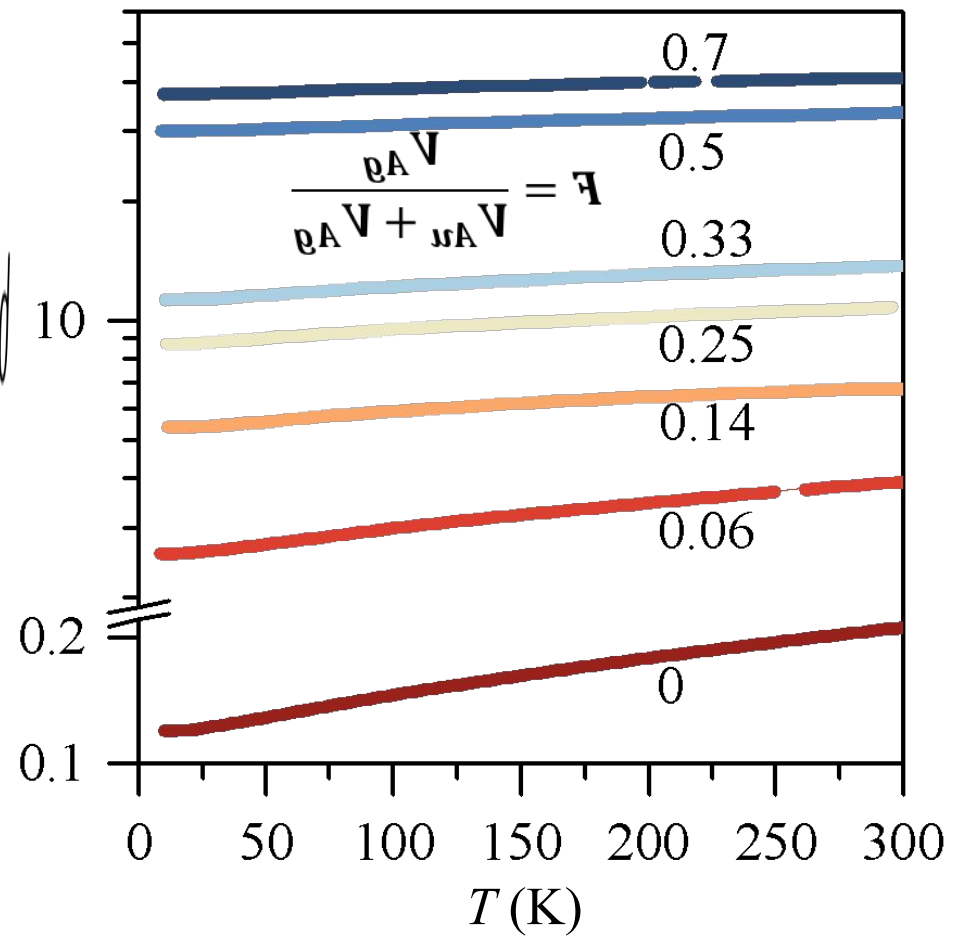


Clustering

Resistivity saturation

The Mott-Ioffe-Regel (MIR) Limit and 'bad metals'

MIR Limit: $k_F l = 1$ $\rho_{MIR}^{Au} = 24.6 \mu\Omega\text{-m}$



□ Saturation in T-dependent resistivity close to the MIR limit

Bound in the residual resistivity (disorder) in the range $F \sim 0.4 - 0.8$ towards the MIR limit